COMPUTER AIDED DESIGN OF FERRO-ELECTRIC INSULATORS

BY

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A THESIS

SUBMITTED TO THE DEPARTMENT OF ELECTRICAL AND ELECTRONIC ENGINEERING IN PARTIAL FULFILMENT OF THE REQUIREMENTS

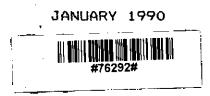
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ABSTRACT

Computer aided design of ferro-electric insulators is mostly a theoretical method of designing insultors. With the help of computer and some analytical techniques some of the conventional insulators are analyzed.

First the electromechanical stress distribution for ferroelectric material was calculated using finite element method. In order to formulate the finite element method, the region between two circular parallel plates has been divided into a finite number of triangular elements. An extremum function in energy density form can be developed. Then using energy minimization technique, the potential at different vertices of the elements can be calculated.

A computer program has been developed for calculating electric field and electromechanical stresses for ferro-electric material placed between two circular parallel plates. The program can be readily used for designing ferro-electric insulators subject to variable electromechanical stresses.

COMPUTER AIDED DESIGN OF FERROELECTRIC INSULATORS

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LIST OF PRINCIPAL SYMBOLS

Ë.	Electric stress or field vector (Volts/m)
ā	Electric flux density (Coulomb/m²)
P	Charge density (Coulomb/m ³)
٤r	Relative permittivity
٤.	Permittivity of free space (Farad/m)
Φ	Potential (Volts)
J	Extremum function
Sc	Element submatrix
ŝ	Electromechanical stress tensor
Sij	Components of tensor S
: ī	Unit column vector
F	Electro-mechanical force (Newton)
n	Unit outward normal to a surface or contour
P	Polarization (Coulomb/m²)
Ŧ	Electro-mechanical stress vector (N/m²)
Pr	Remanant polarization (Coulomb/m²)
Ero	Dielectric constant at very weak field
Ē.	Saturation electric field of ferro-electric material (Volts/m)
Ē	Applied Electric field (Volts/m)

CHAPTER 1

GENERAL INTRODUCTION

GENERAL INTRODUCTION

1.1 Importance of Insulators:

any typical part of power system we can see that it In comprises four types of materials namely. :conductors, insulators, magnetic materials and structural materials. Undoubtedly, the most complex of the four are the insulators. Its duty is to ensure the safe operation of diverse power components as large generators, power transformers, power capacitors, circuit breakers , overhead transmission lines and underground cables. The insulator has twofold functions one for insulating and the other for giving mechanical support for the live parts of power system equipment under any possible circumstances in field as wind, snow, rain, contamination, earthquake and so on. such Therefore, it is not too much to say that reliability of power system depends upon the quality and reliablity of insulators.

1.2 Brief literature review:

In order to reduce the losses in power system the trend of increasing transmission voltage is increasing day by day. So for obtaing a reliable power system we need more reliable insulators. Increase in voltage causes increase in size of system apparatus. Improvement and compactness of design of system apparatus can reduce the cost and saving of energy resources. Moreover, the insulators' are used for electrical insulating purpose as well as for mechanical support and the potential applied to it causes electrical and mechanical stresses. So for optimising and to get a reliable insulator it should be designed to withstand higher electromechanical stresses.

The insulation technology has *reached the present position after a long years of study and research. In high voltage insulators space charge and its distribution can cause undesireable effects. Various effects of Space charge **1**n insulators have been summarised by leda [1]. He showed that the developed space charge alters the distribution profile of the field in comparison with the original field. It is known that the formation of space charge depends whether the field is uniform or non-uniform. The measurement of space charge distribution and interficial electric fields are important for understanding the mechanism of charge build-up and decay.

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The study of electric field distribution in and around insulating structures has been of considerable interest to electrical engineers for designing high voltage equipment. The peak stress value in insulating system is an an important parameter to control, because it influences discharge initiation and propagation. Compaction and miniaturizion of high voltage system with resulting increased operating stress levels have made the study of electric stress distribution even more critical. Moreover physical systems are so complex that the analytical solution of Laplace's and Poisson's equations is difficult .But with the incresing availablity of high speed computers (6766) various numerical techniques are being extensively developed for electrostatic fields in high voltage systems. calculatino Mukherjee and Roy [2] calculated fields in insulators using fictitious point charge method and they were successful in applying this method for disc insulators. Chang [3] analyzed the electric stress distribution in cavities embedded within dielectric structures and he shows that the field inside the void enhanced by a factor ε_r , the relative dielectric permittivity i 5 of the insulator, in the case where no free charge is present the void boundary. Takeshi [4] used charge simulation method in combination with the method of image to find electric fields tn dielectric multilayers. Tadasu [5] successfully applied charge

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simulation method to study the field behaviour at points on the boundary of two dielectrics. Takada and Sakai [6] were successful in determining electric fields at the dielectric electrode interface. Kun [7] suggests that the field distribution along the insulator surface is strongly dependent on the ρ -E characteristic as well as frequency of the operating voltage.

High tangential fields causes flashover along insulator surface. To keep tangential field below the limit required for a sustained discharge, the insulator length has to be a minimum value for a given voltage rating. Abdel-Salam [8] found that to optimize a high voltage insulator, the distribution of the tangential field component along its surface should be uniform.

Stih [9] formulated a classical approach to high voltage insulating system design using an integral equation technique for solving electric fields and optimizing the contours of the insulator.

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1.3 Present state of art of the project

All porcelain or ceramic insulators used in high voltage power system as well as telephonic and telegraphic lines are ferro-electric insulators. These insulators are mostly designed testing for mecannical breakdown stress and electrical by flashover tests. No rigorous mathematical solutions for such design is available. A classical approach of designing high voltage insulators was carried by Stih [9] using integral equation techniques for solving electric stress and contour optimization. But if the hysteresis effect arising from ferro-electric property of the material is considered, a rigorous mathematical operation is needed. Begg [10] formulated the electromechanical stress analysis considering the hysteresis effect of ferro-electric materials.

1.4 Objective of the research:

The objective of this study is to evaluate the electromechanical stress distribution associated with the time periodic electric fields applied on ferro-electric insulators of finite size and to obtain an acceptable design in terms of breakdown stress, flashover voltage and electrostriction.

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1.5 Research outline:

To design a high voltage insulator, electromechanical stress calculation is the first step. In doing so, the insulator region will be divided into finite nos. of trangular subregions called elements. Then the potential distribution and electromechanical stresses can be obtained using finite element method and developing an energy distribution function in variational form for the system under consideration.

CHAPTER 2

FERRO-ELECTRICITY AND INSULATORS

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FERRO-ELECTRICITY AND INSULATORS

2.1 Introduction:

In dielectric material an applied electric field induces dipole moments in atoms or ions and generally displaces ions relative to each other. Consequently the dimension of a specimen undergoes slight changes. Mechanical stresses also change the dimensions of a specimen but in general such changes do not produce a dipole moment. In other words, in most materials dielectric polarization produces a mechanical distortion, but a mechanical distortion does not produce polarization. This electro-mechanical effect, which is present in all materials, is called electrostriction [13].

Ferro-electric materials are characterised by electrostriction arising from their spontaneous or residual polarization. There are various types of ferro-electric materials that are used in high voltage insulators because of their high relative permitivity. Barium titanate (BaTiO₃) is an important ferro-electric material that is used in fabrication of high quality AC and DC insulators used in HV power transmission.

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2.2 Ferro-electricity

For the dielectric material the polarization is a linear function of the applied field. There are however, a number of substances for which the polarization of a specimen depends on its history i.e. the polarization in these materials is not a unique function of the field strength. These materials exhibit hysteresis effect, similar to those observed in ferromagnetic materials - they are therefore called ferro-electric materials [13].

An example of a hysteresis loop associated with the polarization versus electric field strength is given in fig. 2.1, when an electric field is applied to a "virgin" specimen of a ferroelectric material, the polarization increases along a curve OABC. When the field is reduced, it is observed that for $E_0 = 0$, a certain amount of remanent polarization, Pr is still present.

In other words, the material is spontaneously polarized. In order to make polarization to zero, a field in the opposite direction must be applied; this field is called the coercive field, Ec.

The direction of spontaneous polarization is generally not the same throughout the macroscopic specimen. In fact, the specimen may be considered to consist of a number of domains which are themselves spontaneously polarized but with the direction of polarization varying from one domain to another.

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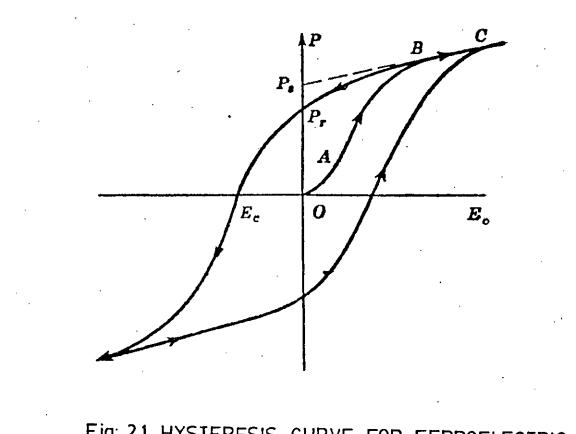


Fig: 2.1 HYSTERESIS CURVE FOR FERROELECTRIC MATERIAL

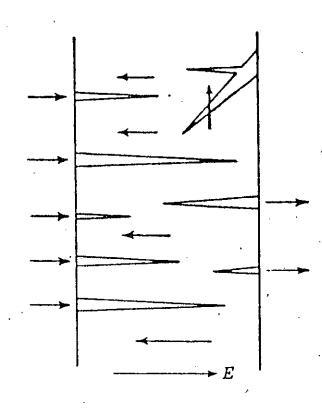


Fig: 2.2 DOMAINS SHOWING POLARIZATION

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Thus a virgin macroscopic specimen may have zero polarization as a whole. Upon application of an electric field, the domains for which the polarization points along the direction of the applied field grow at the expenses of other domains for which the polarization points in the other direction (Fig 2.2).

Barium titanate (BaTiO₃) is the best known ferro-electric material commonly used in the fabrication of HV insulators/ capacitors with multilayered structure. Their high permittivity enables fabrication of capacitors with high capacitance and insulators with good quality. There are three types of BaTiO₃ materials commonly used in insulators. These are NPO ($\varepsilon_r = 60$), X7R ($\varepsilon_r = 1800$) and ZSU ($\varepsilon_r = 9000$). The permittivity of ferroelectric materials depend on the temperature. A typical temperature dependence of BaTiO₃ ceramic is shown in Fig.2.3.

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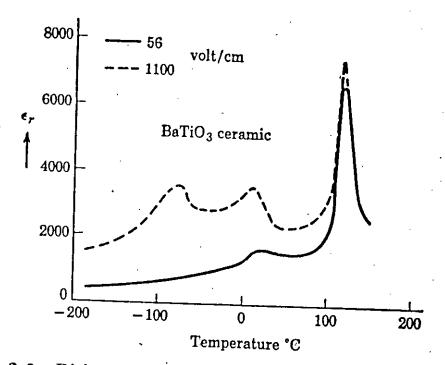


Fig. 2.3. Dielectric constant of barium titanate ceramic as a function of temperature. The fully drawn and the dashed curves correspond respectively to a peak field strength at 1 kc of 56 and 1100 volts per cm. The sharp peaks occur at the ferroelectric Curie temperature θ_f .

2.3 Ferro-electric insulators

The material most commonly used for high voltage insulators is porcelain. It has high insulating resistivity and undergoes hysteresis effect with the application of electric fields. So,we can say that most of the high voltage insulators are manufactured from ferro-electric materials. The dielectric strength of mechanically sound porcelain insulator is of the order of 12KV/mm to 28KV/mm. The ultimate strength of such insulator is for compression 275 KN and for tension 20 KN. Though the tensile strength is lower but most of the insulators are designed in such a way that it undergoes compressive stresses most of the time.

The second material that is used in manufacturing high voltage insulators is glass. Though it has higher dielectric strength, ultimate tensile strength, higher puncture voltage but due to the surface errosion and contamination problem these are not popular. In porcelain insulator these problems are overcomed by suitable design.

Insulators are required to withstand both mechanical and electrical stresses. In addition to this, the surface leakage path, even when wet, must have sufficiently high reistance to prevent any appreciable current flowing to earth. So , the insulators must have enough leakage distance. For obtaining sufficient leakage distance and type of application different types of insulators are used in high voltage system. In the following articles some of them are discussed.

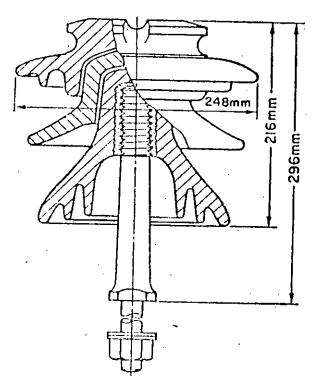
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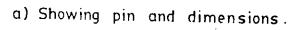
2.3.1: Pin-type Insulators.

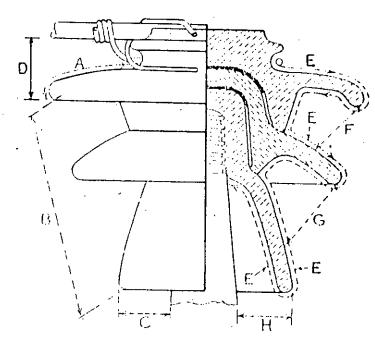
Pin-type insulators are of one piece construction and used operating voltages up to 33KV. As the name suggests, the pin for type insulator is attached to a steel bolt or pin which is screwed to the cross arm on the pole or tower. There is a groove on the upper end of the insulator for housing the conductor. The conductor passes through this groove and it is bound by the annealed wire of the same material as the conductor. They are preferred by some users, even at voltages where multi-part insulators are available, because of the comparative absence of cement. An adequate length of leakage path is obtained by the provision of two or three sheds. There should be sufficient thickness of porcelain between the line conductor and the insulator pin to give a factor of safety of up to 10 against puncture. The insulator is designed in such a way that it will sparkover before it punctures. At wet and contaminated condition the sheds becomeQ conducting and to avoid sparkover the pin should be sufficiantly long.

The insulator and its pin should be sufficiently strong mechanically to withstand resultant force due to the combined effect of weight of span, wind pressure etc. For higher voltages, the thickness of the insulator is to_A^{bo} increased, so, it becomes uneconomic. That is why pin type insulators is used up to voltage level of 33KV. A schematic diagram is shown in fig 2.4.

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b) Showing flashover distance

Fig: 2.4. Pin Type Insulator

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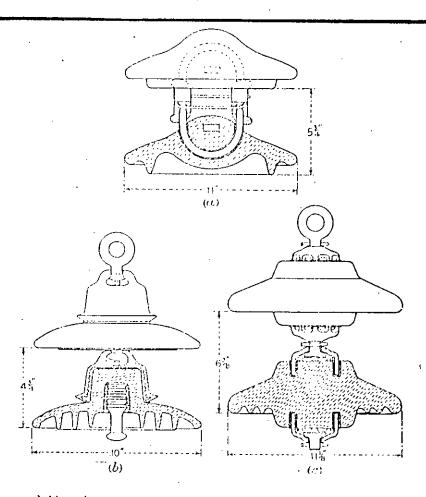
2.3.2: Disc-type Insulators.

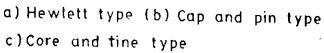
Disc-type insulators are very popular for constructing high voltage lines because of their relatively smaller size and less weight. Each disc is designed for a comparatively low working voltage and the required total insulation is obtained by using a string of suitable number of such insulators. The mechanical stresses on the insulator is less as the insulators are connected flexibly with the tower.

The first disc insulator is the Hewlt type (fig 2.5) and is characterized by great simplicity of design. Each unit consists of a single piece of porcelain, the central portion of which has two curved tunnels laying in planes at right angles to each other. The short steel strips, forming the connectors between individual units, are threaded through these tunnels and thus loop through each other, bending separated by layer of porcelain which is wholly in compression. This method of construction secures a high mechanical strength and there is no risk of breakage by the difference in expansion of conducting links and insulators.

In cap and pin type or cemented cap disc type insulators shown in fig 2.5^b, each unit is covered by a metal cap cemented in place, the upper end of each cap terminating in a lug to which the pin of the unit above is fastened. The pins are also cemented in place and consecutive discs are joined together by ball and socket joints. The three materials porcelain, cement and steel

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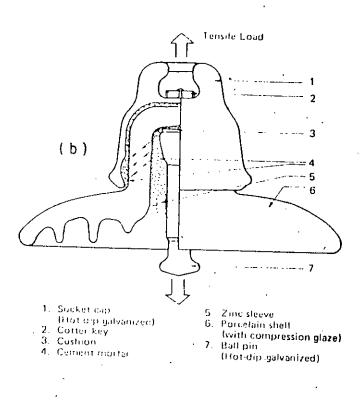


Fig: 2.5. Disc Type Insulator

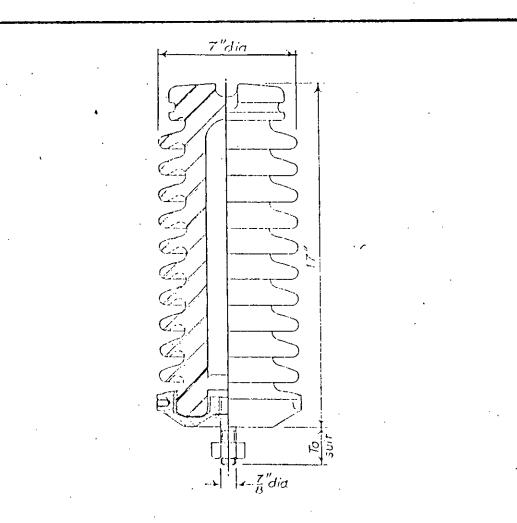
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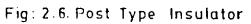
have different co-efficients of expansion and sudden temperature change in service were sufficient to set up internal bursting stresses, which ultimately cracked the insulator. The cement material is subjected to volumetric changes depending on its moisture content and causes fracturing process. Improvements in design overcomes these troubles and cap-and pin disc insulator is giving an excellent survice in all parts of the world.

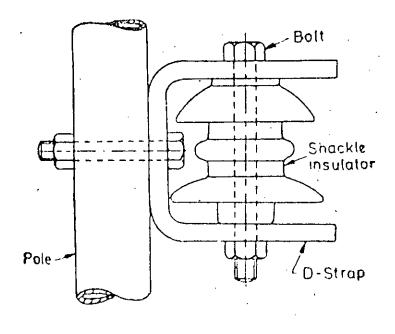
Another type of disc insulator is core and time insulator as shown in fig 2.5. Each insulator disc is symmetrical and conforms approximately the lines of electric field thus avoiding materials of different permittivities being placed in series. The metal work consists of pressed steel spiders, the legs of which are fastened into the porcelain. It is not easy to produce the necessary thick porcelain discs. That is why the core and time insulators have fallen into disuse.

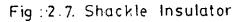
2.3.3: Post Insulators:

The post type insulators are very much important for constructing high voltage switching equipments and protection equipment. These are used in constructing the breaking chamber of MOCB, transformer and circuit breaker bushing, current transformers, potential transformer etc. In some places this type of insulators are used as line insulator up to 30KV. A schematic diagram of post type insulator is shown in fig 2.6.









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The post type insulator() is of solid core or hollow construction as per use and have a cylindrical boundary shape. All the metal work and cement is external to the porcelain. So it cannot set up bursting stress. The sheds are designed in such a way that it can be cleaned efficiently by rain. Moreover its great advantage is that if the sheds are broken off by power arc or mechanical damage, the flashover voltage of the insulator is little effected. So, this type of insulator is very useful.

2.3.4: Shackle Insulators.

Shackle Insulators are mostly used in distribution lines . Such insulators can be used either in a horizontal position or vertical position. They, can be fixed directly on the pole as shown in fig 2.7. The conductor is fixed in the groove with a soft binding wire.

2.3.5: Problems With Conventional Insulator

safety and reliablity of transmission lines depend on . The long term performance of insulators. the Insulators must electrically and mechanically remain stable for a long period of service under harsh environmental conditions such as contamination, wind, rain, snow and so on. So, the insulators must be designed in such a way that it must cope with harsh environmental conditions. Some special designs against different causes of insulator detoriation are discussed bellow:

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a) Aging of insulating material:

Poor manufacturing technique causes internal defects in the insulating material, resulting in cracking or shattering due to mechanical or electrical stress concentration on the defects during a long term use. The porosity of porcelain occurs due to improper firing technique and reduces electrical and mechanical strength. Improved manufacturing technique together with good quality of insulating material can reduce this problem .

b) Contamination and Erosion of Insulating Materials

A drastic reduction can be seen in withstand or flashover voltage when the insulator surface is contaminated and wetted. The pollutant accumulation, cleaning of polluted surface, wetted of pollutant layer, leakage current and occurence of flashover are influenced by the insulator shape, dimensions, atmospheric conditions, voltage stress, pollution source etc. This contamination problem is severe in the coastal and desert area. In heavy contaminated environment, the surface detoriation of insulating material occurs due to surface errosion, in the worst case, resulting complete failure of insulating material. The errosion is caused by leakage current on the insulators.

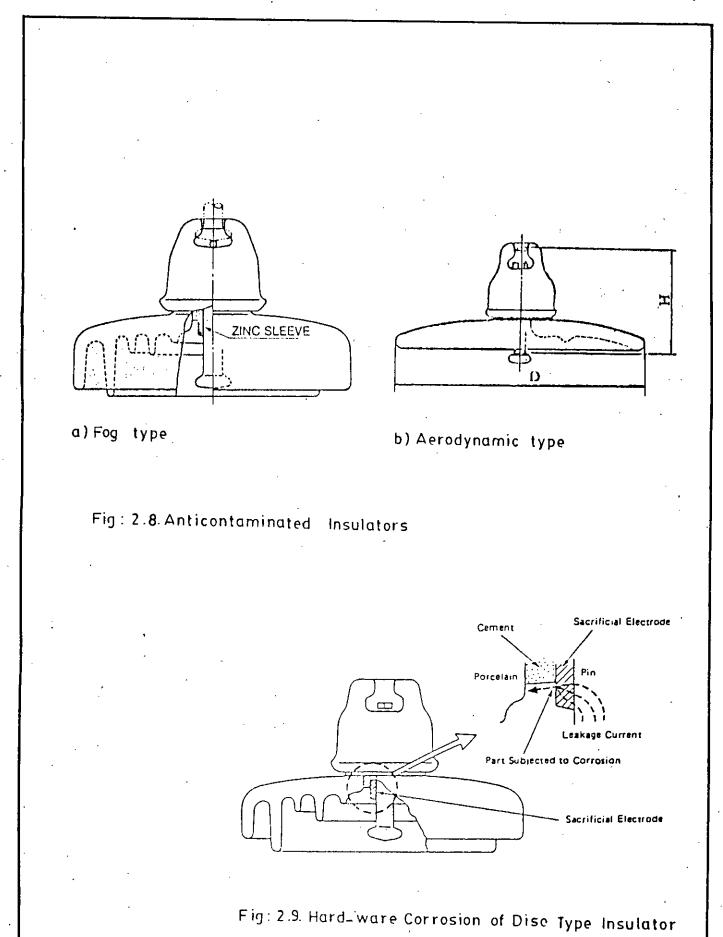
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The anti-contaminated insulators are designed to provide less contaminant accumulation on surface, to keep surface dry and to increase the leakage distance. There are BOMe anticontaminated designs of disc type insulators namelv aerodynamic or profile type and fog type insulators as shown in fig 2.8. In aerodynamic type insulators the leakage distance is 300 to 400 mm and the shape is such that the contamination is cleaned by the wind. In fog type insulators, inner skirts are long enough to provide long creepage distance and remain dry and less contaminated condition as these are covered by the top skirtrs.

c) Cement Growth Failure.

In cap-and-pin disc insulator the cap and the pin 16 fitted to the insulator by cement. The cement is usually dried and hardened after curing, resulting in shrinkage but it sometimes causes also expansion of its volume by enough water. Moreover, its properties changes with time. Accordingly, the cement changes and expands with time and a high mechanical stress is applied to the material of the suspension insulators. This in causes radial cracks in the pin hole. Laboratory tests on turn various insulators support the mechanism for cement growth as being mainly due to excessive gypsum present in the cement. Not all the cements used in the assembly of insulators exhibit this long term expansion.

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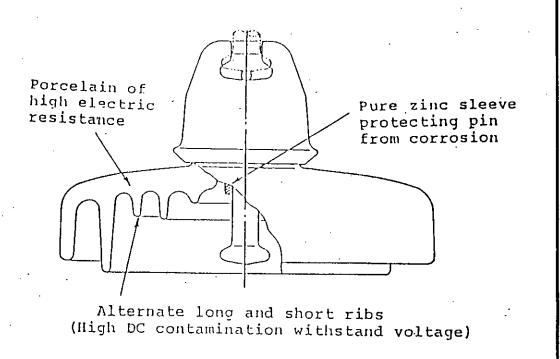
d) Hardware corrosion.

The hardware of suspension insulators also suffers from corrosion during long term use in contaminated areas. In both AC and DC lines, this corrosion presents due to the electrochemical reaction (electrolytic corrosion) because of the flow of leakage cureent as shown in fig 2.9. Among hardware of suspension insulators, pin corrosion is serious problem because of reduction in mechanical strength of the corroded pin or breakage of insulator caused by expansion of pin body. The pin can be protected against electrolytic corrosion by attaching a sacrigical electrode (Zink Sleeve) to the pin close to cement boundary as in fig 2.9.

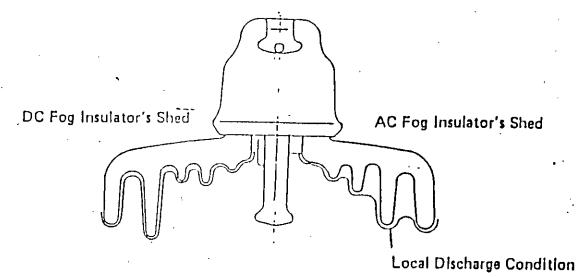
2.3.6: D.C Insulators:

Recently, DC transmission line became popular due to the availability of DC converting equipment and for long distance transmission of bulk power. As the DC flashover mechanism is different from AC ones, so the insulators used in DC line should be of different shape than AC ones, otherwise fault rate will The insulator under DC voltage is more contaminated increase. than under AC voltage due to the dust collecting effect of DC voltage. Moreover the local discharge effect is more effective in DC insulators. So it is clear that the surface errosion, pin corrosion and flashover problems are more severed than AC insulators.

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a) Insulator Unit Showing Different parts



b) Showing Discharge

Fig 2.10 D.C Insulators

In order to cope with the above problems, the DC insulators are usually manufactured by high electric resistance porcelain putting a zinc sleeve around the pin shank and for obtaining high withstand voltage the shed is designed with alternate long and short ribs, keeping long distance between rib lips and long leakage distance as shown in fig. 2.10. The DC insulators are desinged to provide 10-20% higher withstand voltage than AC insulator with same leakage distance.

2.4 Discussion

From the above discussion we can say that the ferroelectric insulators are the widely used and most popular insulator. In both AC and DC power system they are most reliable. Glass insulator), the other material used in manufacturing HV insulator, presents high local discharge of contaminated condition, which in turn causes surface errosion and pin corrosion and lowers the mechanical strength. In ferroelectric insulators this is not so prominent. Due to the high insulating resistance local discharge is less in this type of the insulators. The ferro-electric materials have high compressive stress and low tensile stress. For that most of the ferroelectric insulators are designed to bear high compressive and low tensile stress. Disc insulators, the widely used insulators, are designed taking this into consideration.

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CHAPTER 3

THEORETICAL ASPECTS OF DESIGNING FERRO-ELECTRIC INSULATORS

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THEORETICAL ASPECTS OF DESIGNING FERRO-ELECTRIC INSULATORS

3.1 Introduction:

Physical system comprises of different types of dielectrics, such as solid, liquid and gaseous dielectrics and in almost every instance a combination of at least two of these components is involved. Another observation is that the dielectric must frequently serve as a structural material as well as an insulating material. Liquid and gaseous dielectric may also serve as coolants. These double or sometimes triple functions causes mechanical and thermal stresses in addition to electrical stress and place severe constraints on the designer, which greatly reduce his freedom of choice. This is because he has to consider a multiple system of stresses, such as electrical, mechanical and thermal stresses.

The electrical stress on the insulation of a power system Component is perhaps the easiest to quantify. Firstly, there is stress due to the steady state power frequency voltage. Depending upon the perticular component involved, this may range from a few Kv up to 800 Kv, with higher voltages in contemplation. Because of the geometry of most power system components, the electric fields that voltages give rise to, are more often than not quite non-uniform.

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In addition to the power frequency fields, system insulation is subjected to transient overvoltages caused by switching operations and intrusion of lightining into the power system. Those are of variable duration, magnitude and wave form. Rapidly changing transient voltages can temporarily cause further extremely non-uniform distributions of stress.

So, the study of electric field distribution in and around insulating structures has been of considerable interest to electrical engineers for designing equipment that operate at very high voltage levels. The peak stress value in an insulating system is an important parameter to control because it influences discharge initiation and propagation. Compaction and miniatuarization of high voltage system, with the resulting increased operating stress levels, have made the study of electric stress distribution even more critical.

Mechanical stress occurs due to mechanical deformation under the application of electric fields. Thermal Stresses occur due to the thermal gradients, which present in insulators due to the ohmic losses in the conducting parts.

Unfortunately, the excessive electrical, mechanical and thermal stresses often occur simultaneously. And as thermal stress is not so prominant, Then electro-mechanical stress analysis is very important for an insulating system design.

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present analysis is, however, motivated to the calculation of electro-mechanical stress developed in ferroelectric material. But electro-mechanical stress analysis of such media has not been reported. Only the electro-mechanical

stress in ether, a hypothetical medium has been widely discussed by stratton [11]. Taking this analysis into consideration as valid for dielectric, we extended that analysis for fermelectric materials.

3.2 Evaluation of Potential Distribution by Finite Element Method.

The basic principle used for developing finite element method of finding potential distribution is the solution of Laplace's equation. Laplace's equation is written as

> $\nabla \dot{\Phi} = 0$ (3.1)

where $\Phi = potential$

Our

Physical systems are so complex that the analytical solution of Laplace's equation is very difficult, though not impossible. As such, with the increasing availability of high speed digital computers, two numerical methods are being extensively used in the calculation of electrostatic fields in high voltage systems.

The first method is based on the difference technique employing Laplace's and Poisson's equations in the space where the field is to be determined. This is done by dividing the whole space into small meshes.

The second approach to the computation of fields is to integrate Laplace's or Poisson's equation either by employing discrete charges, or by dividing the electrode surface into sub-sections with charges. This method of computation is known as the charge simulation method. In this method fictitious point, line or ring charges are assumed outside the space in which the field is to be computed. The magnitude and position of these charges are such that their integrated effect together with the field of those charges existing inside the space, satisfies the boundary conditions. This method is very successful for many high voltage field problems.

Finite element numerical technique is now being extensively used to find solution of Lapace's equation encountered in problems related to civil, mechanical and electrical engineering, chang ©et© al[3]used finite element method to calculate electrical stress distribution within dielectric cavities. The finite element method is a powerful numerical technique that can be precisely used to solve boundary value problem by piecewise linearization of the potential function over a large number of discrete spatial elements. In this chapter we are formulating the finite element method of solving laplace's equation to obtain electrical stress distribution.

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The basic requirement of the development of finite element equation is to find an() extremum function which can be written in energy density form. As a first step in the development of this method , a uniform surface is considered which is completely filled with homogeneous and isotropic dielectric.

The extremum function for electrostatic field can be written as,[10]

$$J(\Phi) = \frac{1}{2} \iint \nabla \Phi |_{ds}^{2} \qquad \dots \qquad (3.2)$$

The finite element method employs a set of algebric functions defined over a subsection of the whole crosssection. These subsections may be polygonal in shape and are called elements. Thus in the finite element method the entire domain over which the operator is defined is divided into a finite number of elements on each of which the actual node function is approximated by a set of continious algebric functions which are only defined over the particular element under consideration and are linearly dependent on the values of ϕ at the vertices of the element.

Hence , if an element has n vertices (for triangular element n=3), the potential Ψ within it may be approximated by [10]

$$\varphi(\mathbf{x},\mathbf{y}) = \sum_{m=1}^{n} (\mathbf{x},\mathbf{y}) \Phi_{m} \qquad (3.3)$$

Where Φ_{m} is the value of Φ at the vertex m and Nm(x,y) is a predetermined algebric function which is uniquely defined and differentiable over the element and which reduces to zero outside the element.

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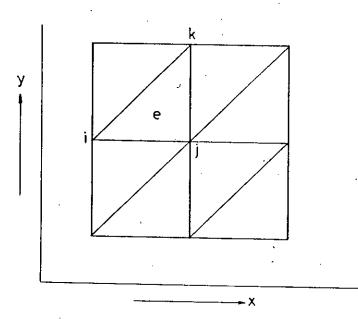


Fig 3.1 : division into triangular elements

Let us consider triangular elements as shown in fig 3.1. A typical element (the eth element) is described by the vertices i,j and k in cyclic order. Let \mathbb{R} , \mathbb{R} and \mathbb{R} be the corresponding values of \mathfrak{P} at the vertices. For the element e the functional dependence of $\mathfrak{P}(x,y)$ can be written as [10]

$$\Phi(x,y) = \alpha_0 + \alpha_1 x + \alpha_2 y \qquad (3.4)$$

where α_0, α_1 and α_2 are to be determined.

If (x_1, y_1) , (x_2, y_2) and (x_1, y_2) are the coordinates of the vertices i, j and k, then solving for α_0, α_1 and α_2 , we obtain, [10]

$$\begin{aligned}
\Psi(x,y) &= \frac{1}{2A} + b_{x,x} + c_{x,y} \Psi_{L}^{e} + \frac{1}{2A} + b_{y,x} + c_{y,y} \Psi_{J}^{e} \\
&+ \frac{1}{2A} + \frac{1}{2A} + b_{k,x} + c_{k,y} \Psi_{L}^{e} + \dots \quad (3.5)
\end{aligned}$$

- 34 -

Where 2A is the determinant of the matrix,

$$\begin{bmatrix} 1 & \chi_{\pm} & y_{\pm} \\ 1 & \chi_{\pm} & y_{\pm} \\ 1 & \chi_{\kappa} & y_{\kappa} \end{bmatrix}$$

A = area of the triangular element.

$$a_{1} = \chi_{1} \cdot y_{k} - \chi_{k} \cdot y_{k}$$
$$b_{1} = y_{3} - y_{k}$$
$$c_{1} = \chi_{k} - \chi_{3}$$

Here ai, bi, ci.... are the cofactors of the above square matrix.

From (3.5) we get ,

$$\frac{\partial \Phi^{e}}{\partial X} = \frac{1}{2A} \qquad (3.6)$$

$$\frac{\partial \Phi^{e}}{\partial Y} = \frac{1}{2A} \qquad (3.7)$$

Now from equation (3.2) for eth element,

$$J = \frac{1}{2} \iint \left[\left(-\frac{\partial \Phi}{\partial X} \right)^2 + \left(-\frac{\partial \Phi}{\partial y} \right)^2 \right] dx \cdot dy$$

$$= --- \int \int \left[\left(b_{1} + b_{1} + b_{2} + b_{3} + b_{4} + b_{5} + c_{4} + c_{5} + c_{5$$

Since
$$\frac{1}{2} \iint dx \cdot dy = A$$

$$J = \frac{1}{---} [(b_{1} \oplus_{i}^{e} + b_{3} \oplus_{j}^{e} + b_{k} \oplus_{k}^{e})^{2} + (c_{1} \oplus_{i}^{e} + c_{3} \oplus_{j}^{e} + c_{k} \oplus_{k}^{e})^{2}]$$

$$BA$$

$$(3.8)$$

If there are in all M vertices, then from (3.2)

$$J(\Phi) = F(\Phi_{1}, \Phi_{2}, \Phi_{3}, \Phi_{4}, \dots, \Phi_{n})$$
 (3.9)

The optimum value of a set of \mathfrak{P}_m for a certain functional form of Nm(x,y) may be obtained by minimizing the function given by (3.9) with respect to each of m i.e. equating,

$$\frac{\partial J}{\partial \phi_m} = 0$$
; for $m = 1, 2, 3$... M (3.10)

However, in the vicinity of boundaries where constants

$$J \xrightarrow{1}{\longrightarrow} P_b^2$$

So that at the boundary, $\frac{\partial \mathfrak{I}}{\partial \Phi} \longrightarrow \Phi_{b}$

where $\mathcal{P}_{\mathbf{b}}$ is the value of the potential at the boundary.

)

Using equation (3.10) for the minimization of J function over the element e.

$$\frac{\partial J}{\partial P_i} = \frac{1}{4A} \left[b_1 \varphi_1^{e_1} + b_2 \varphi_2^{e_1} + b_k \varphi_k^{e_1} \right] + c_1 \left(c_1 \varphi_1^{e_1} + c_2 \varphi_2^{e_1} + c_k \varphi_k^{e_1} \right) \right]$$

$$\frac{\partial J}{\partial \Psi_{j}} = ---[b_{J}(b_{1} \Psi_{1}^{e} + b_{J} \Psi_{j}^{e} + b_{k} \Psi_{k}^{e}) + c_{J}(c_{1} \Psi_{1}^{e} + c_{J} \Psi_{j}^{e} + c_{k} \Psi_{k}^{e})]$$

$$4A$$

$$\frac{\partial J}{\partial \Psi_{\kappa}} = \frac{1}{4A} + \frac{\partial \Psi_{1}}{\partial \Psi_{1}} + \frac{\partial \Psi_{2}}{\partial \Psi_{1}} + \frac{\partial \Psi_{1}}{\partial \Psi_{\kappa}} + \frac{\partial \Psi_{\kappa}}{\partial \Psi_{\kappa}} + \frac{\partial \Psi_{\kappa}}{\partial$$

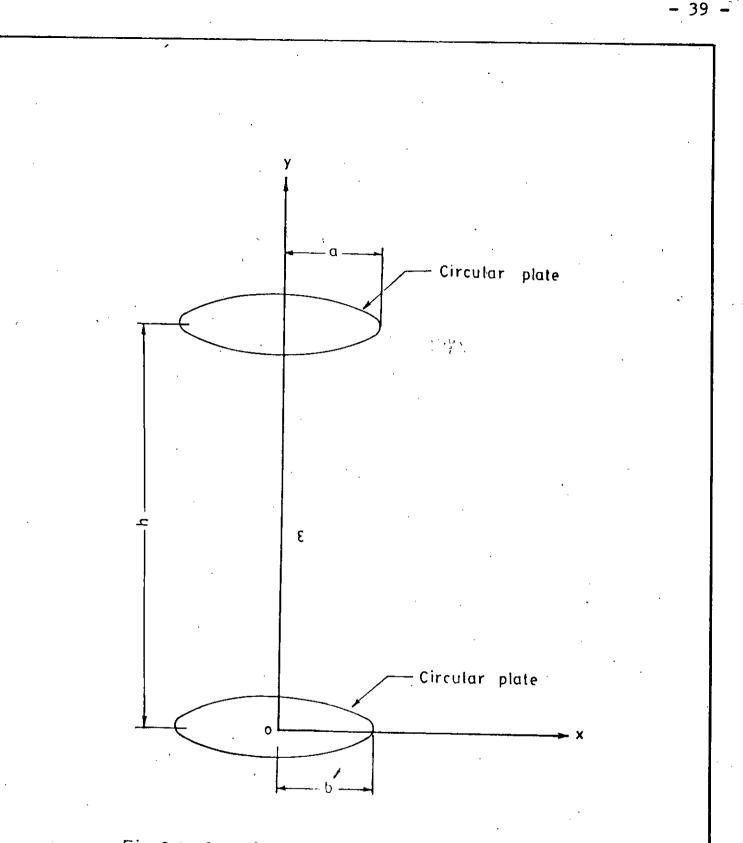
In matrix form for the element with nodes i, j and k

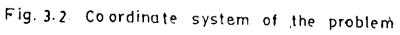
<u>96</u> 92	$b_i^2 + c_i^2$ $b_i \cdot b_j + c_i \cdot c_j$ $b_i \cdot b_k$	+ C1+CH	Pi
$\frac{\partial J^{e}}{\partial \mathfrak{P}_{3}} = \frac{1}{4A}$	$b_{1},b_{2} + c_{1},c_{3} = b_{2}^{2} + c_{3}^{2} = b_{3},b_{4}$ $b_{1},b_{4} + c_{1},c_{4} = b_{3},b_{4} + c_{3},c_{4}$	+ CJ.Ck	P; ^e
<u>94</u> 92	$b_{1} \cdot b_{R} + c_{1} \cdot c_{R} b_{3} \cdot b_{R} + c_{3} \cdot c_{R}$	b ² κ + c ² κ	PK
or, -3	$\frac{1}{\Phi^e} = \left[\mathbf{s}^e \right] \left[\Phi^e \right]$	ب • • •	⊢ ⊣ (3.11)

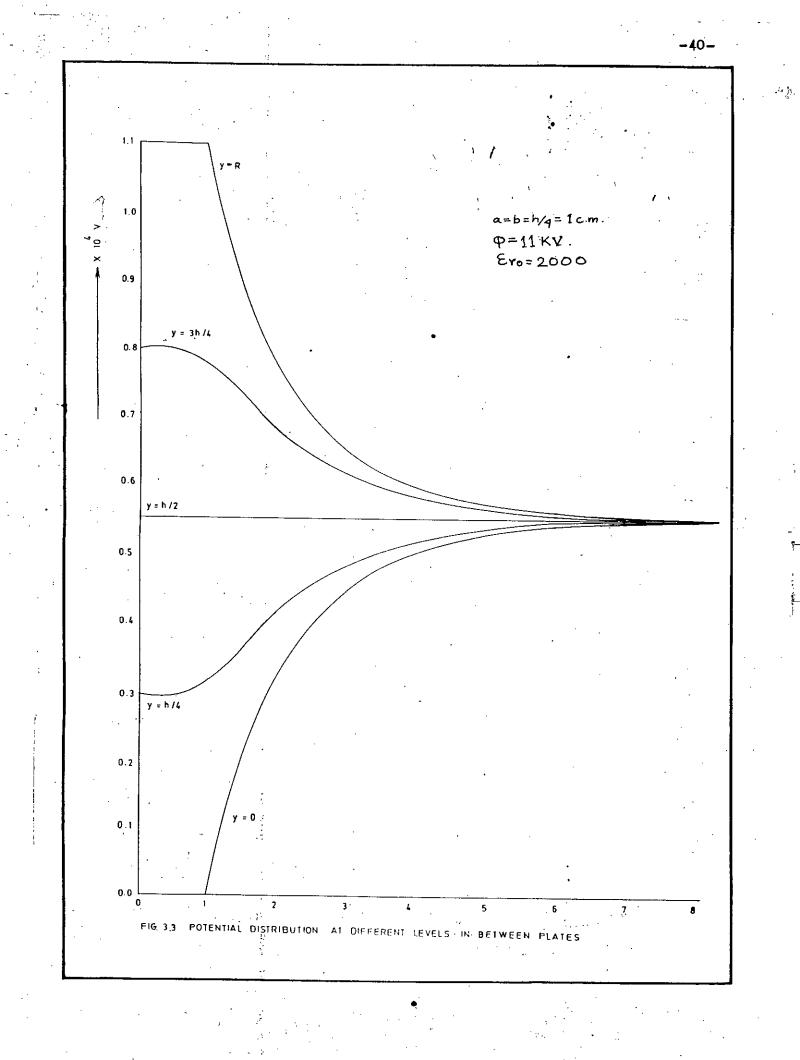
Where S^m is the element sub-matrix and Ψ^e is a column matrix. S^m is a square symmetric matrix such that $B_{i,j} = B_{j,i}$. The above equation can be applied to obtain elemental submatrices for all the elements of the domain. The resultant matrix will be the sum of all the element submatrices generated by all the elements. Then inverting this matrix and multiplying it with the boundary values we can get the potentials of the nodes of each element The potential distribution for parallel circular thin plate as shown in fig 3.2 can be easily determined by using the above analysis.

Let the upper plate be kept at a certain potential V = 11KVand the lower plate is maintained at zero potential. The space on one side of Y-axis between the two plates is divided into 64 numbers of elements and 45 nodes. Assuming linear variation of potential over elements, taking permittivity is constant over the region and considering the procedure discussed earlier we get 45 linear algebric equations. Solving these equations we oet potentials at different nodes. The results are polotted in fig 3.3. From the plot it is clear that the potential is constant about the level Y = h/2, the potential from the top plate decreases gradually and become constant function of x at the level Y = h/2 i.e. $\Psi = (5.5 \text{KV})$. Similarly from the bottom plate the potential gradually increases and becomes a constant function of x at Y = h/2 i.e., mid level. Thus at Y = h/2 $\frac{\partial \Phi}{\partial x} = 0$ indicates that no lateral field exists. Rather the field is entirely vertical at the midlevel between the two plates. This is expected because the electric lines of forces emanating from the top plate will turn towards the bottom plate after reaching vertically at the mid level.

This also indicates that half of the energy is stored in the upper half region as is expected in a parallel plate capacitor or in the case of dipole.







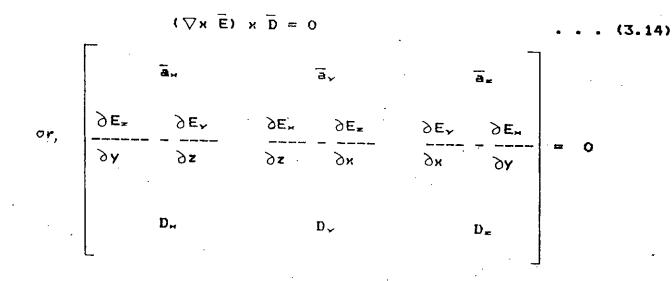
3.3 Electromechanical Stress Analysis

The theory of Maxwell-Faraday on electromechanical stress in "ether" has been widely discussed by Stratton [11]. Emphasizing their validity for dielectric materials, the following analysis has been done.

Let us suppose that a certain bounded region of space contains charge distribution. The field is produced in part by the charges within the region and in part by the sources which are exterior to it. Then at every interior point we get,

$$\overline{E} = -\nabla \mathcal{P}$$
Then $\nabla \times \overline{E} = 0$... (3.12)
and $\nabla \cdot \overline{E} = \frac{\rho}{\varepsilon}$... (3.13)

Let equiltion (3.12) be multiplied vectorically by $\overline{D} = \mathcal{E}_{\mathcal{E}} \overline{\mathcal{E}}_{\mathcal{A}} \overline{\mathcal{W}} \overline{\mathcal{E}}$ get,



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The x,y and z components of the vector (3.14) are given by,

$$C(\nabla \times \overline{E}) \times \overline{D} = D_{z} (---- - ----) - D_{y} (----- - ----) = 0 \dots (3.15)$$

 $E(\nabla \times \overline{E}) \times \overline{D} \cdot \overline{a}_{Y} = D_{X} \left(\frac{\partial E_{Y}}{\partial x} - \frac{\partial E_{Y}}{\partial y} - D_{z} \left(\frac{\partial E_{Y}}{\partial y} - \frac{\partial E_{Y}}{\partial z} \right) = 0 \dots (3.16)$

 $E(\nabla \times \overline{E}) \times \overline{D}]. \xrightarrow{a_z} D_y (---- - ---) = D_x (---- - ----) = 0 \dots (3.17)$ $\frac{\partial E_z}{\partial y} \frac{\partial E_z}{\partial z} = \frac{\partial E_z}{\partial z} - \frac{\partial E_z}{\partial x}$

The above equations can be arranged by adding equal quantities on both sides.i.e,

$$\frac{\partial E_{x}}{\partial z} = \frac{\partial E_{z}}{\partial x} = \frac{\partial E_{y}}{\partial z} = \frac{\partial E_{y}}{\partial y} + E_{x} \nabla \cdot \overline{D} = E_{x} \nabla \cdot \overline{D}$$
(3.18)
$$\frac{\partial E_{y}}{\partial x} = \frac{\partial E_{x}}{\partial y} - \frac{\partial E_{z}}{\partial y} + E_{y} \nabla \cdot \overline{D} = E_{y} \nabla \cdot \overline{D}$$
(3.19)

 $\frac{\partial E_{v}}{\partial x} = \frac{\partial E_{x}}{\partial y} = \frac{\partial E_{x}}{\partial z} + E_{z} \nabla \cdot \vec{D} = E_{z} \nabla \cdot \vec{D} = (3.20)$

The above three equations can be arranged in tensor form,

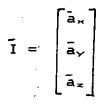
$$\nabla \cdot \mathbf{SI} = \mathbf{E} \nabla \cdot \mathbf{D} \qquad \cdots \qquad (3.21)$$

where \hat{S} is the tensor expressed as follows:

<u>~</u> -

		S ₁₂	513	
s =	5 ₂₁	522	523	• • • (3.22)
	S31	S32	Saa	

and I is the column vector expressed as,



For an isotropic dielectric the elements $S_{1,j}$ are shown in Table 3.1.

	j/k	1	2	3
	1 .	€.6.4E ² - <u>€.6</u> 7 _{E²} 2	ᢄ₀ᢄ ӻ⋿ఄఀ _ఀ ⋿ _⋎	€ ₈ € ₇ E _∞ E _∞
· · · ·	2	⋩_•⋩ ŗ⋿ _⋎ ⋿	E.Er E ² - <u>E.E</u> r _{E² 2}	€ ₽₽₽₽₽₽
	3	E,E _E_K	⋵_⋴⋸ _⋎ ⋿ _⋇ ⋿ _⋎	E.E.F.E.Z - E.E.F.E.Z

Table 3.1 : Components Sid of the tensor \hat{S} in free space

Equation (3.21) is a relation through which the forces exerted on elements can be expressed in terms of the vector \tilde{D} . As $\nabla \cdot \tilde{D}$, is the charge density is in column/m³, the force distribution given by the right hand side of (3.21) will be in Newton/m³. Let us now integrate the identity over a volume V to obtain the force,

$$\tilde{F} = \int \nabla \cdot \hat{S} I dv = \int \tilde{E} \nabla \cdot \tilde{D} dv$$

Let \bar{n} be the unit outward normal at a point on the boundary surface. Then by divergence theorem.

$$F = \oint (\hat{SI}).nda = \int \bar{E} \nabla \bar{D} dv$$

(3.23)

Thus the quantity $(\widehat{SI}).\overline{n}$ comes out in the form of force per unit area or as mechanical stress. That means $(\widehat{SI}).\overline{n}$ represents a mechanical stress developed with application of electric stress \overline{E} . In vector notation the electromechanical stress is given by

$$t = (\hat{SI}) \cdot \hat{n}$$
 ... (3.25)

Hence the stress components can be given as,

$$t_{x} = (S_{11}\overline{n}_{x} + S_{12}\overline{n}_{y} + S_{13}\overline{n}_{z})$$

$$t_{y} = (S_{21}\overline{n}_{y} + S_{22}\overline{n}_{y} + S_{23}\overline{n}_{z})$$

$$t_{z} = (S_{31}\overline{n}_{x} + S_{32}\overline{n}_{y} + S_{33}\overline{n}_{z})$$

Referring to Fig.3.2 the electric field between the two circular parallel plates has x and y components only. Now if we desire to calculate stress in the xz plane then \overline{n} will be in the y direction such that $\overline{n}_x = 0$, $\overline{n}_y = 1$ and $\overline{n}_z = 0$.

Then

$$\mathbf{t}_{\mathsf{M}} = \mathbf{S}_{12} = \mathcal{E}_{\mathsf{n}} \mathcal{E}_{\mathsf{m}} \mathbf{E}_{\mathsf{M}} \mathbf{E}_{\mathsf{M}}$$

. (3.26)

(3.27)

$$t_{\gamma} = S_{22} = \mathcal{E}_{e}\mathcal{E}_{r} (E_{\gamma}^{2} - --E^{2})$$

$$= \frac{E_{*}E_{*}}{2} (E_{*}^{2} - E_{*}^{2})$$

 $t_z = S_{32} = 0$

. . (3.28)

Hence the magnitude of the stress is given by,

$$t = \sqrt{t_{\pi}^{2} + t_{\gamma}^{2}}$$

$$= \xi_{\sigma}\xi_{\gamma}\sqrt{(E_{\pi}E_{\gamma})^{2} + \frac{1}{-4} - (E_{\gamma}^{2} - E_{\pi}^{2})}$$

$$= \frac{\xi_{\sigma}\xi_{\gamma}}{2} (E_{\pi}^{2} + E_{\gamma}^{2})$$

$$= \frac{\xi_{\sigma}\xi_{\gamma}}{2} E^{2}$$
or,
$$t = -\frac{1}{-4} - D_{\tau}E$$
... (3.29)

The angle of the mechanical stress is then given by

$$\theta_{m} = \tan \begin{pmatrix} t_{\gamma} \\ ---- \\ t_{m} \end{pmatrix} \qquad (3.30)$$

1 _____ In general --- D.E represents the magnitude of the electro-2 mechanical stress in the dielectric.

3.4 Electromechanical Stress Distribution in Ferroelectric Material between Two Thin Circular Parallel Electrodes.

In order to obtain the electromechanical stress distribution in ferroelectric material between two thin circular parallel electrodes by finite element method, first we have to calculate the applied field distribution between the electrodes. The applied field can be expressed as,

$$E_{o} = \overline{a_{x}}, E_{ox} + \overline{a_{y}}, E_{oy}$$

The field components E_{ov} and E_{ov} can be easily obtained by dividing the region between the electrode into finite number of triangular elements and applying equations (3.6) and (3.7) we get,

$$E_{GK} = ---- [b_1 \mathcal{P}_i^{e} + b_2 \mathcal{P}_j^{e} + b_k \mathcal{P}_k^{e}] \qquad ... (3.32)$$
2A

$$E_{e_{k}} = ---- [c_{1} q_{1}^{e} + c_{1} q_{2}^{e} + c_{k} q_{k}^{e}] \qquad ... (3.33)$$
2A

(3.31)

mean For satisfying the_Ahysteresis curve (Fig. 2.1) the magnitude of the electric flux density as a function of electric field can be well approximated as,

 $D = \mathcal{E}_{o} (\mathcal{E}_{ro}, \mathcal{E}_{o} - \mathcal{K} \mathcal{E}_{o}^{3})$. (3.34)

Where $\delta_{s}\delta_{s}=----$

Hence, \mathcal{E}_{ro} is the dielectric constant at very weak field, K is a constant.

ferroelectric material When is placed between two electrodes, major portion of the electrical energy is spent in polarizing the molecules. After polarizing the dielectric, a portion the supplied energy remains to link the two of electrodes. These phenomena are explained by Lorentz equation.

 $\overline{\mathbf{D}} = \overline{\mathbf{D}}_{\mathbf{n}} + \overline{\mathbf{P}}$ (3.35)

Where.

P is the polarized portion,

and $\overline{D}_{o} = \mathcal{E}_{o}\overline{\mathbb{E}}_{o}$ is the macroscopic flux density that remains as unpolarized portion of the net flux density D. The purpose of an electrical insulation is to keep this unpolarized flux density to a minimum. As $\nabla \cdot \vec{D}_{\alpha} = 0$ in the dielectric region, then $\vec{E}_{\alpha} = -\nabla \Psi$, where Φ is the potential satisfying Laplaces's equation and can be obtained by the finite element method discussed earlier.

from (3.34) and (3.35) we get Now $P = \mathcal{E}_{o} \left[\left(\mathcal{E}_{ro} - 1 \right) \mathcal{E}_{o} - \mathcal{K} \mathcal{E}_{o} \right]$

. . (3.36)

The effective relative permittivity Er is obtained from

D1

After saturation the field leaks out into the medium sourrounding the ferroelectric material, and flashover takes place around the insulator with the air breakdown at which the field strength is, Es = 2×10^6 v/m. We choose Ec = 1/2 Es = 10^6 v/m and ε_{ro} = 2000 for ceramic at 100°C (the extreme condition).

Now from equation (3.34) we can also write the x and y components of flux density as,

$$D_{x} = \boldsymbol{\xi}_{\bullet} (\boldsymbol{\xi}_{\uparrow \bullet} \boldsymbol{E}_{o x} - \boldsymbol{K} \boldsymbol{E}_{o x}^{3}) \qquad (3.42)$$

$$D_{\gamma} = \xi_{\bullet} (\xi_{\tau_0} E_{\sigma\gamma} - K E_{\sigma\gamma}^{3}) \qquad (3.43)$$

Again for any dielectric, the internal field developed is given by [11],

$$\vec{E} = \vec{E}_{o} + \vec{E}_{o}$$

where \overline{E}_{o} = applied field

 $\overline{E_{P}}$ = field due to polarization

For ferroelectric material we have $E_{p} = \frac{3\overline{p}}{\varepsilon_{o}}$, where \overline{P} is the polarization vector.

Therefore,

$$\vec{E} = \vec{E}_{a} + \frac{\gamma}{\varepsilon_{a}}$$

 ϑ is a constant, for BaT10₃ the coefficient of expansion $\lambda = 3 \times 10^{-5}$ per degree and the observed curie constant $1/\lambda \vartheta \cong 10^{5}$. Hence $\vartheta \cong 1/3$ [13].

Again for ferroelectric material the polarization is expressed as, [13]

$$\frac{\partial P}{\partial E_{o}} = \mathcal{E}_{o}(\mathcal{E}_{P} - 1) \qquad (3.45)$$

Where $\hat{E}_{\mathbf{y}}$ is the relative permitivity of the material. For polarization in x and y direction we can write,

$$\frac{\partial P_{x}}{\partial E_{ox}} = \mathcal{E}_{o} (\mathcal{E}_{yx} - 1)$$

$$\frac{\partial P_{y}}{\partial E_{oy}} = \mathcal{E}_{o} (\mathcal{E}_{yy} - 1)$$

$$(3.46)$$

$$(3.46)$$

(3.44)

<u>(</u> 50 -

where \mathcal{E}_{rx} and \mathcal{E}_{ry} are the relative permittivities for fields in x and y direction respectively. Now by definition of relative permittivity,

Hence substituting the values of flux density components from equations (3.42) and (3.43) we get,

$$\mathcal{E}_{rx} = (\mathcal{E}_{r_0} - 3KE_{ox}^2)$$
 ... (3.49)

$$\mathcal{E}_{ry} = (\mathcal{E}_{r_0} - 3KE_{er}^2)$$
 . . . (3.50)

Substituting equations (3.49) and (3.50) into equations (3.46) and (3.47) respectively we get.

$$\frac{\partial P_{n}}{\partial E_{on}} = \mathcal{E}_{o} \left(\mathcal{E}_{ro} - 1 - 3 \mathsf{K} \mathsf{E}_{on}^{2} \right) \qquad \dots \qquad (3.51)$$

$$\frac{\partial P_{\nu}}{\partial E_{\mu\nu}} = \mathcal{E}_{\nu} \left(\mathcal{E}_{\nu\nu} - 1 - 3KE_{\mu\nu}^{2} \right) \qquad (3.52)$$

Hence by integrating we get,

$$P_{H} = \mathcal{E}_{0} E (\mathcal{E}_{r0} - 1) E_{e_{H}} - K E_{e_{H}}^{3}] . . . (3.53)$$

$$P_{\gamma} = \mathcal{E}_{0} \mathbb{E} (\mathcal{E}_{\gamma_{0}} - 1) \mathbb{E}_{\sigma_{\gamma}} - K \mathbb{E}_{\sigma_{\gamma}}^{3} 1 \dots (3.54)$$

Now substituting equations (3.53) and (3.54) in equation (3.44) we get the components of the field as,

$$E_{x} = [\delta (E_{yo} - 1) + 1] E_{ox} - KE_{ox}^{3} ... (3.55)$$
$$E_{y} = [\delta (E_{yo} - 1) + 1] E_{oy} - KE_{oy}^{3} ... (3.56)$$

3.62)

(3.63)

Therefore the magnitude and angle of the field are

$$E = \sqrt{Ex^{2} + Ey^{2}} \qquad (3.57)$$

and $\theta_{e} = \tan \left(\frac{Ey}{Ex}\right) \qquad (3.58)$

The magnitude of the mechanical stress according to eqn. (3.29) is given by,

The stress t can be divided into x and y components,

$$t^{2} = t_{x}^{2} + t_{y}^{2} = D_{x}D_{y}E_{x}E_{y} + \frac{1}{-4} (D_{y*}E_{y} - D_{x}E_{x})^{2}$$
$$t_{x} = \sqrt{D_{x}D_{y}E_{x}E_{y}} \qquad (3.60)$$

and

$$t_{y} = \frac{1}{2} (D_{y} \cdot E_{y} - D_{x} \cdot E_{x}) \qquad (3.61)$$
$$t = \sqrt{tx^{2} + ty^{2}} \qquad (3.62)$$

and angle $\theta_m = \tan \left(\frac{ty}{tx} \right)$

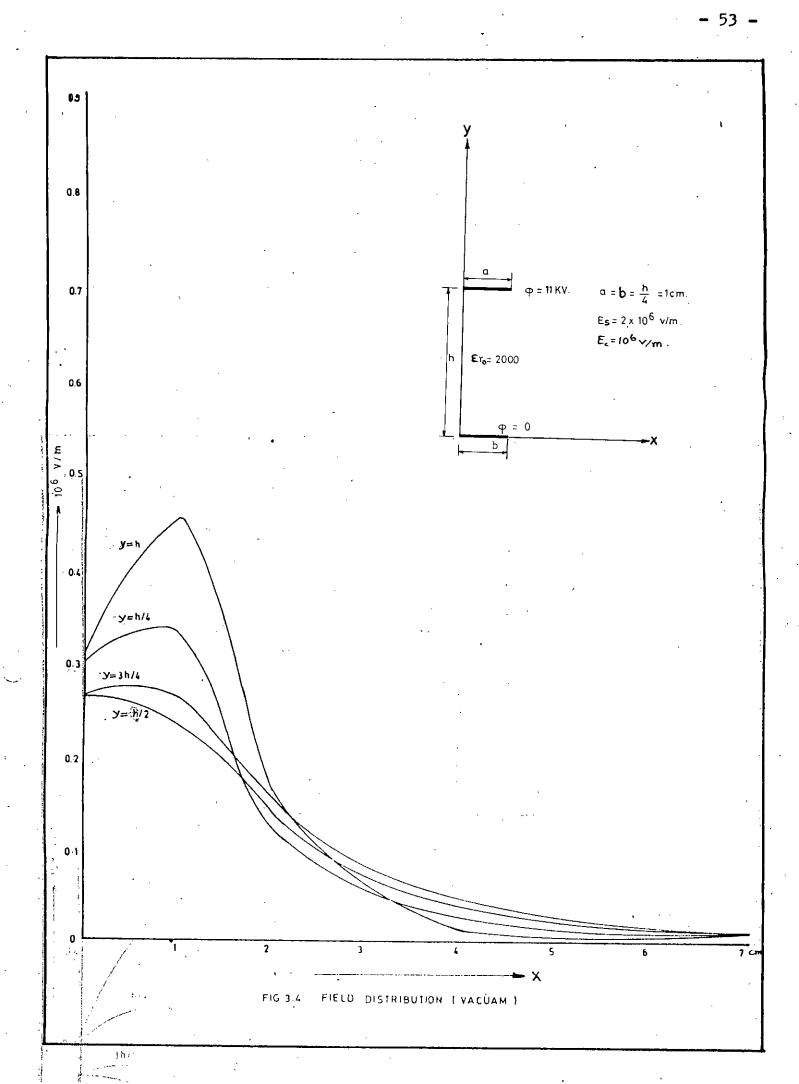
Hence from equation (3.62) and (3.63) we can readily determine the magnitude and angle of mechanical stress developed in ferro-electric material under application of electric field.

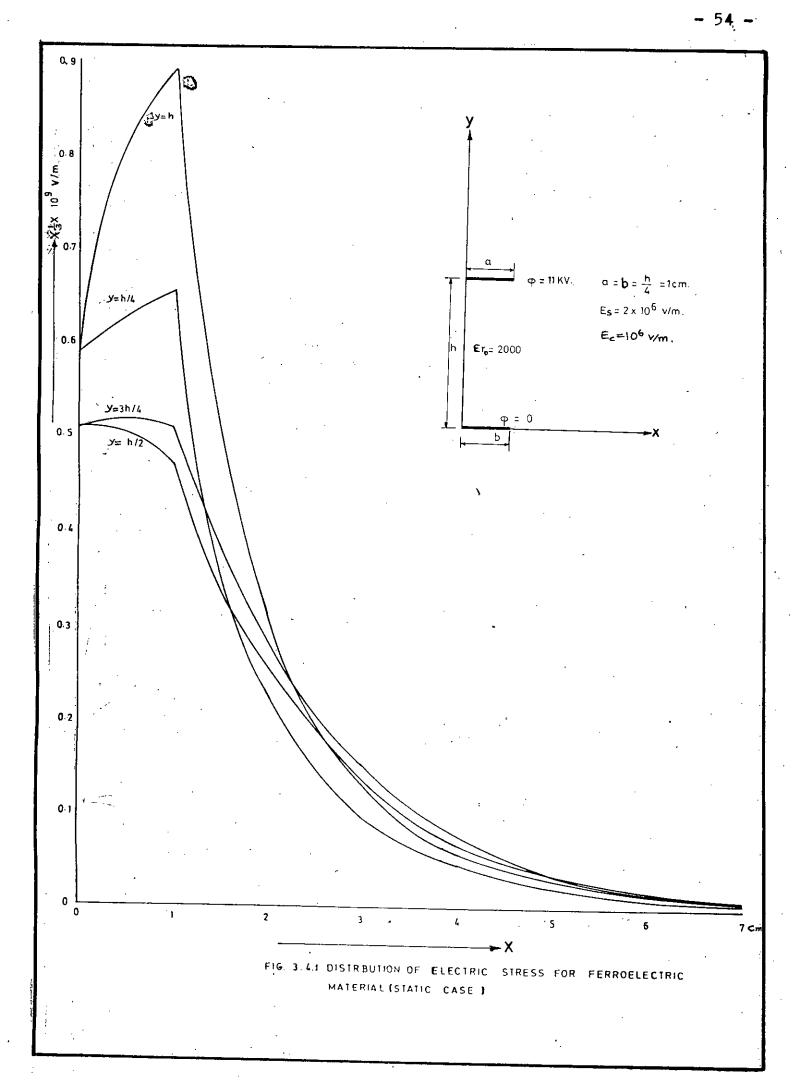
For alternating fields experiencing hysteresis effect, the electric field components in the above expression must be changed as $E_0 \pm E_0$ respectively for alternation from negative maximum to positive maximum and from positive maximum to negative maximum. The coercieve field Ec can be assumed Es/2, where Es is the saturation field.

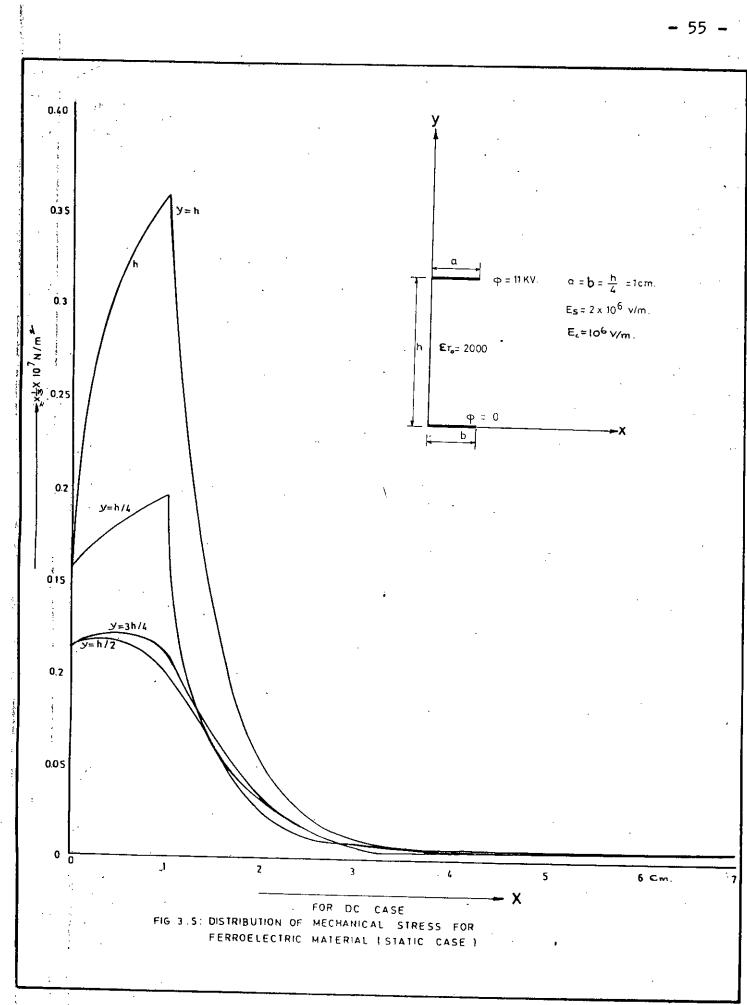
Both the electric and equivalent mechanical stresses have been calculated for ferro-electric material between two circular parallel plates. For electrosfatic case Fig. 3.4 and 3.5 illustrate the plots of electric and equivalent mechanical stress megnitudes as functions of radial distance from the axis of the electrodes. Plots are shown for different levels y=h, 3h/4, h/2 and h/4. The peak values of the stresses occur at the edges of the electrodes and the stress value drops rapidly for distances away from the edge. The electric and equivalent mechanical stress curves have almost similar shape.

From the angle distribution of electromechanical stress shown in table 3.2, it can be checked that the upper half of the ferro-electric material experiences compressive stresses and the lower half of the material experiences tensile stresses.

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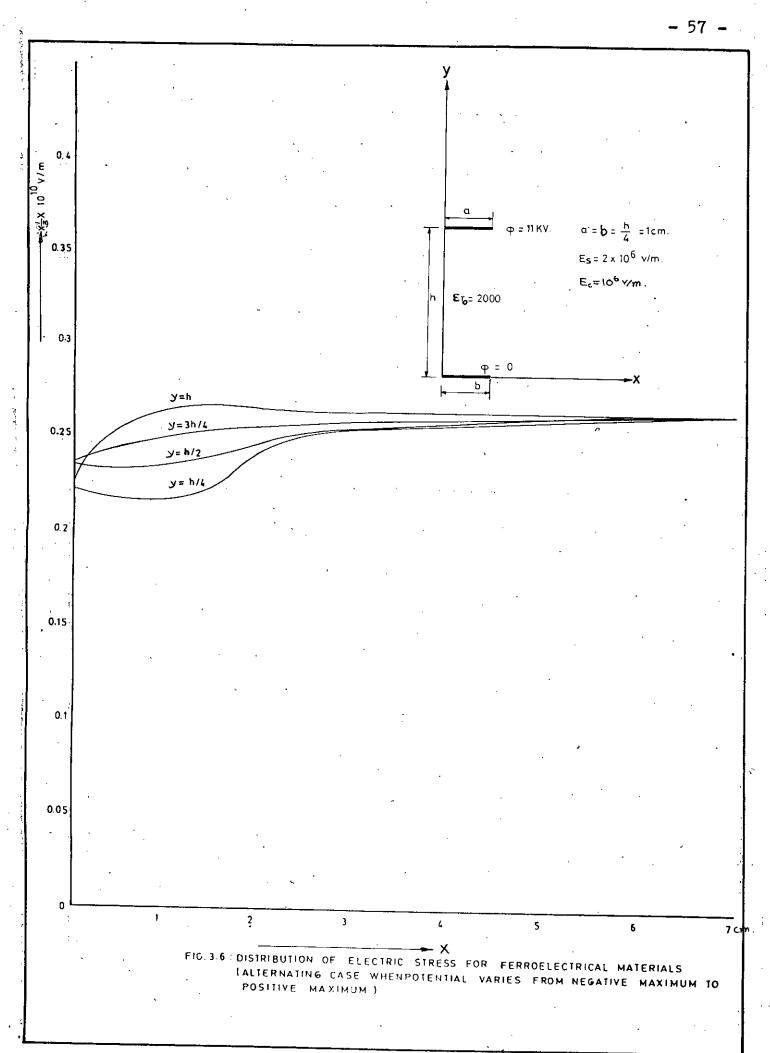
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Electromechanical stress angle variation of ferroelectric material

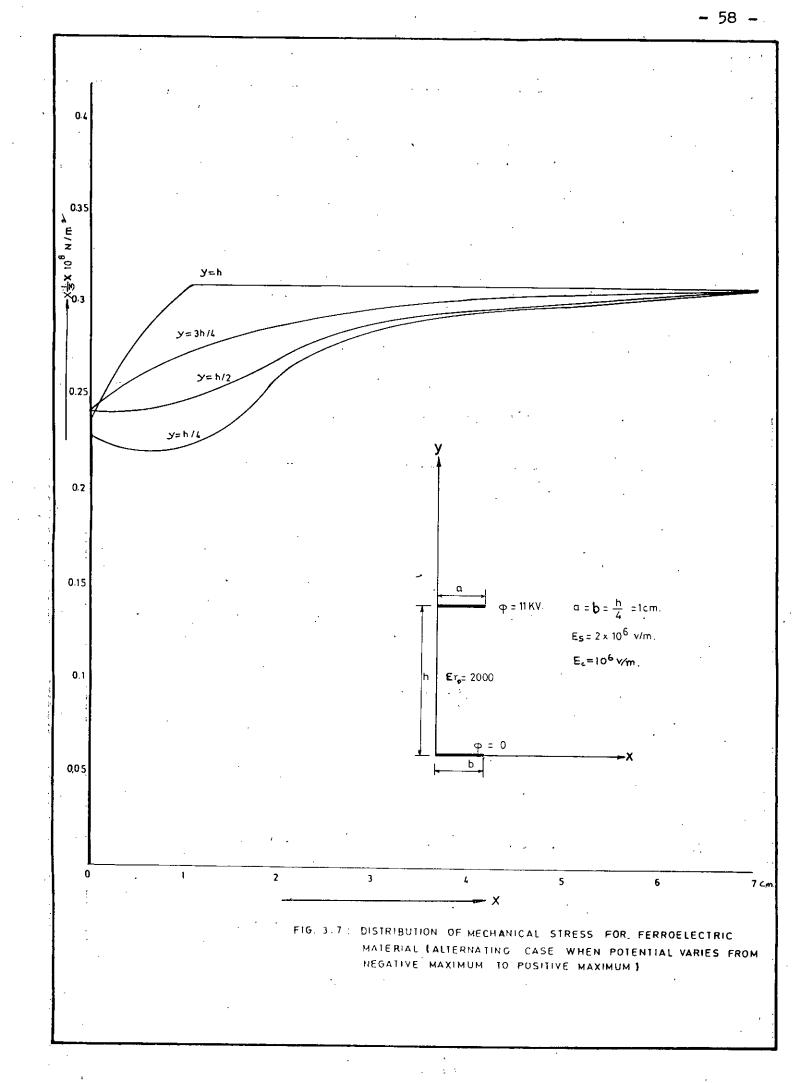
 (Staticase)

Y (C	X (C.m.) (m.)	.) .)`	1	2	- 3	4	5	6	7
4	θe	-90	-44.57	-37.39	-32,96	-30.91	-30.62	-33.43	-52.35
	. Om	+90	-179.153	-164.78	+155.92	-151.83	-151.25	-156.86	-165.28
3	Đe	- 85.41	- 66.48	- 63.64	- 62.80	2.62	- 63.¥4	- 65.89	- 77.25
	θ"	+ 99.17	+137.92	+142.71	+144.39	+144.75	+143.72	+138.20	+115.49
	θe	- 90.00	- 89.99	- 89.99	- 89,99	- 89.99	- 89.99	- 89.99	- 90.00
2	θm	+ 90.00	+ 90.00	+ 90.00	+ 90.00	+ 90.00	+ 90.01	+ 90.00	+ 90
1	θe	- 93.96	-107.96	-124.16	-133.90	-138.29	-139.47	-136.70	-118.48
	. Om	+ 82.074	+ 54.08	+ 21. 6 9	+ 2.19	÷ 6.59	- 8.94	- 3.40	+ 33.02
	θe	-90	-163.07	-164.21	-164.75	-164.83	-164.11	-160.15	-135.00
0	θ"	+90	- 56.139	- 58.435	- 59.507	- 59.66	- 58.23	- 50.31	- 0.01

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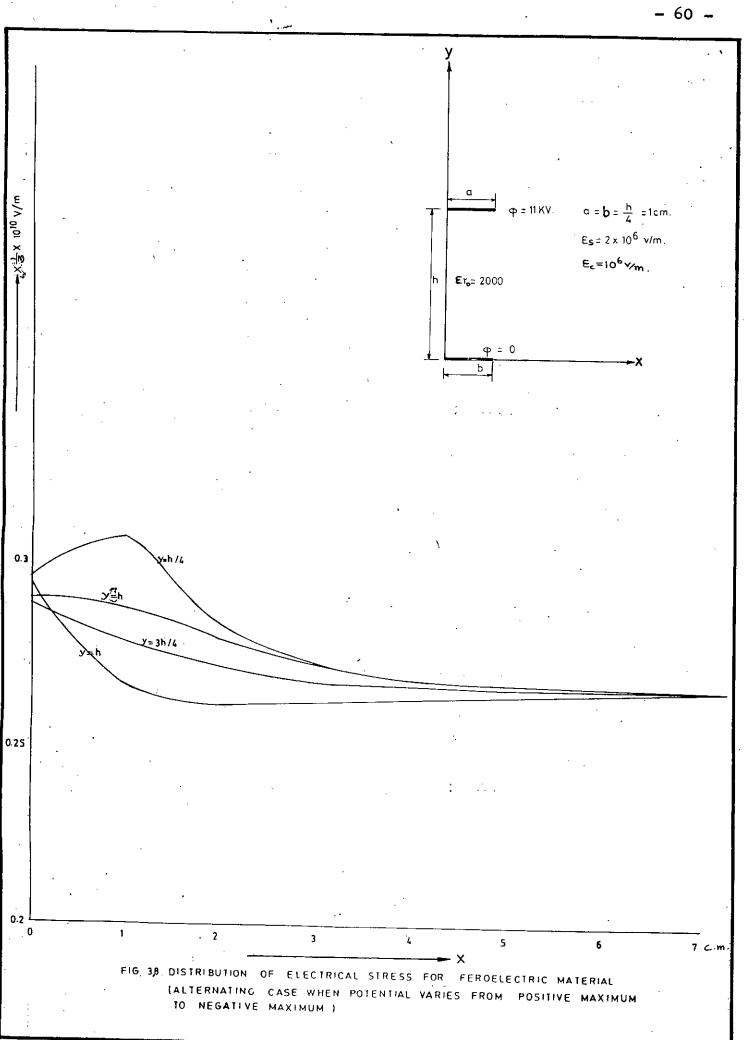


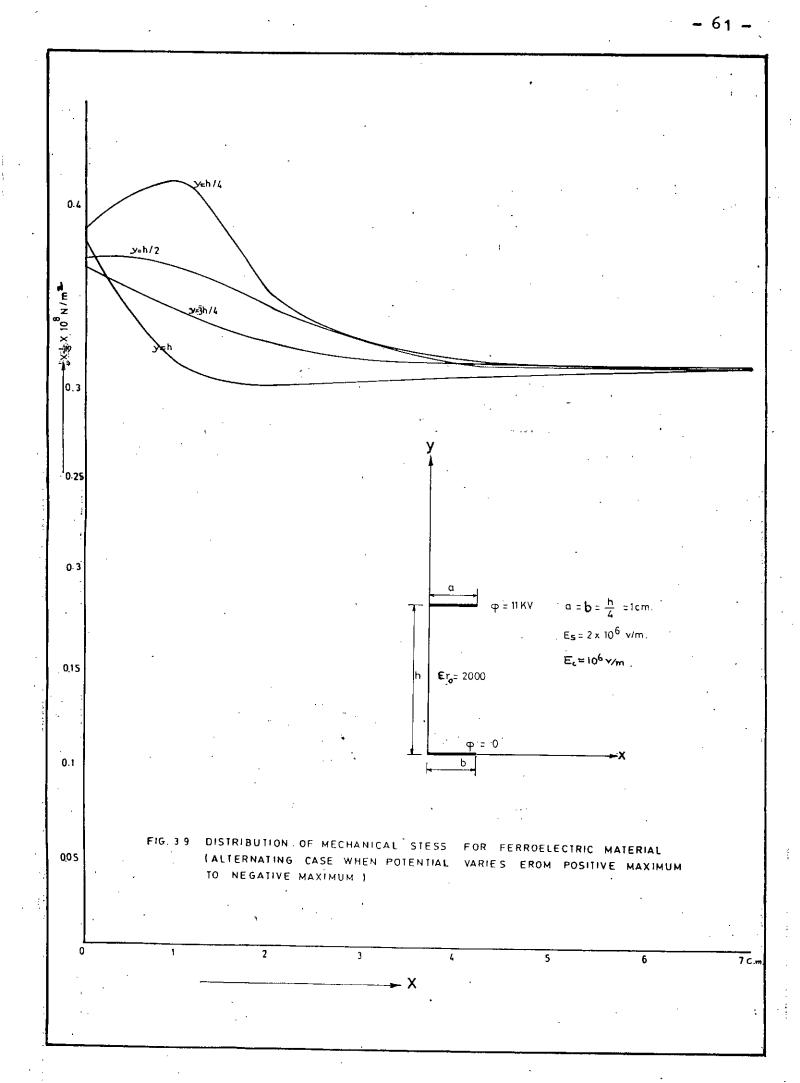
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, 	•		Electro	mechanical st	tress angle ·	variation of	ferrœlectr	ic material	
	•			(Negative r	maximum to p	ositive maxir	num)		· •
	X (C.m.)								
Ү (С.т.)		ò	1	2	3	4	5	6	7
4	θe	+35.10	£9,98	+39.79	+42.85	+44.04	44.56	+44.80	+44.92
4	θ"	-17.42	-30.03	-10.44	- 4.28	- 1.90	- 0.87	- 0.39	- 0.15
3	θe	+37.23	+36.20	+40.03	+42.52	+43.80	+44.43	+44.73	+44.87
	θო	-15.52	-17.59	93	- 4.95	- 2.38	- 1.13	- 0.53	÷ 0.25
2	θe	+37.70	+38,38	+41.51	+43.32	+44.20	+44.62	+44.81	+44.89
. 	θm	-14.59	-13.23	- 6.97	- 3.35	- 1.59	- 0.75	- 0.37	- 0.20
1	θe	+36.75	+38.05	+44.16	+44.96	+45.04	+45.02	+45.00	+44.98
	0m	-16.48	-13.88	- 1.67	- 0.06	- 0.09	- 0.05	- 0.01	- 0.03
0	θe	+35.55	+52.24	+47.44	+46.00	+45.44	+45.19	45.07	45.00
	θm	-18.89	-14.49	- 4.88	- 2.01	- 0.89	- 0.39	- 0.15	0

Table -33
lectromechanical stress angle variation of ferroelectric mate





· .				(Possitiv	re maximum to	negative ma	ximum)		
¥ (c.m.)	(C.m.)		1	.2	3	4	5	6	7
4	θe	-129.29	-119.55	-129.55	-132.79	-134.03	-134.56	-134.80	-134.92
4	θm	+ 11.41	+ 30.22	+ 10.89	+ 4.40	+ 1.93	+ 0.87	+ 0.39	+ 0.15
3	θε	-129.44	-127.71	-130.48	-132.63	-133.85	-134.43	-134.73	-134.87
	θm	+ 11.20	, + 14.57	+ 9.02	+ 4.73	. + 2.33	+ 1.12	+ 0.53	+ 0.25
	θe	-129.93	-130.26	-132.11	-133.47	-134.23	-134-62	-134.81	-134.89
2	θ _m	+ 10.13	+ 9.46	+ 5.76	+ 3.05	+ 1.52	+ 0.74	+ 0.36	+ 0.20
1	θe	-129.76	-131.21	-134.33	-134.96	-135.04	-135.02	-135.00	-134.98
	θm	+ 10.47	+ .5.57	+ 1.32	+ 0.06	+ 0.08	+ 0.05	+ 0.01	+ 0.03
0	θe	-128.98	-175.95	-136.93	-135.91	-135.42	-135.19	-135.07	- 45.00
	θ-	+ 12.02	+ 7.91	+ 3.86	+ 1.82	+ 0.85	+ 0.38	+ 0.15	+ 0

Ta	зb	le	-	3.4

Electromechanical stress angle variation of ferroelectric material

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For alternating field a different nature of stress curve is observed. In the cycle when applied voltage alternates from negative maximum to positive maximum, the stress distribution takes the shape as in Fig. 3.6 and 3.7 and their angle variation is as in Table 3.3. In this case the maximum stress occurs at the edge of the upper plate and the minimum stress occurs at the lower plate. The stress curves attain a constant value with the increase in x. The stress angles in table 3.3 indicate that in this half-cycle the material is subject to laterally expanding stress.

When the applied voltage alternates from positive maximum to negative maximum, the stress distribution takes the shape as in Fig. 3.8 and 3.9 and their angle variation is as in Table 3.4. In this case the maximum stress occurs at the edge of the lower plate and minimum stresses at the upper plate, the stress curves attain constant value with the increase in x. In this case also, the material is subject to laterally expanding stresses as can be checked from the angle distribution shown in table 3.4.

3.5 Discussion.

The above study gives the distribution of electric and equivalent mechanical stresses developed in a ferro-electric material placed between two circular parallel electrodes.

We calculated stresses for both static and alternating fields. In all cases shapes of the electric stress distribution curves resemble those of the equivalent mechanical stress distribution curves.

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For static case the peak stress occurs at the edge of the top plate and minimum stress at the bottom plate. At y = h/2 or i.e. in the mid-level the electromechanical stress has only normal components but the edge of the top plate is subjected to compressive lateral stress only. In general the lower half of the material is subject to expanding stress, the upper half to compressive stresses for a static applied field.

For an a.c. field as the applied potential varies from negative maximum to positive maximum, the peak stress occurs at the edge of the top plate and its magnitude is higher than that of the static stress. The angle variation (Table 3.3) in this case is such that the insulator inside the plates are subject to laterally expanding stresses.

For applied potential varying from positive maximum to negative maximum, the peak stress occurs at the bottom plate and its magnitude is higher than that of the above two cases. So, the greatest maximum stress occurs at the bottom plate. The angle variation (Table 3.4) in this case is such that the insulator inside the plate suffers from laterally expanding stresses.

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CHAPTER 4

DESIGN OF FERRO-ELECTRIC INSULATORS

DESIGN OF FERRO-ELECTRIC INSULATORS

4.1 Introduction:

most obvious objective in insulating system design is The to obtain suitable system elements (electrodes and insulators) which wi11 withstand electrical and equivalent mechanical stresses at normal operating conditions and occasional faults. In order to get reliable insulating system, the peak value of the stresses must be less than the allowable stress. The continuously increasing voltage level of HV devices imposes the need for better space utilization. For this purpose it is necessary to apply electrode and insulator contour optimization in insulating system design. This contour optimization of field distribution and its application in insulating system design is widely discussed by Stih [9]. The same method was discussed by Itaka and Hara [12] for three dimensional field problems. In order to produce high quality insulator, it is necessary to follow some noticed points which are as follows:

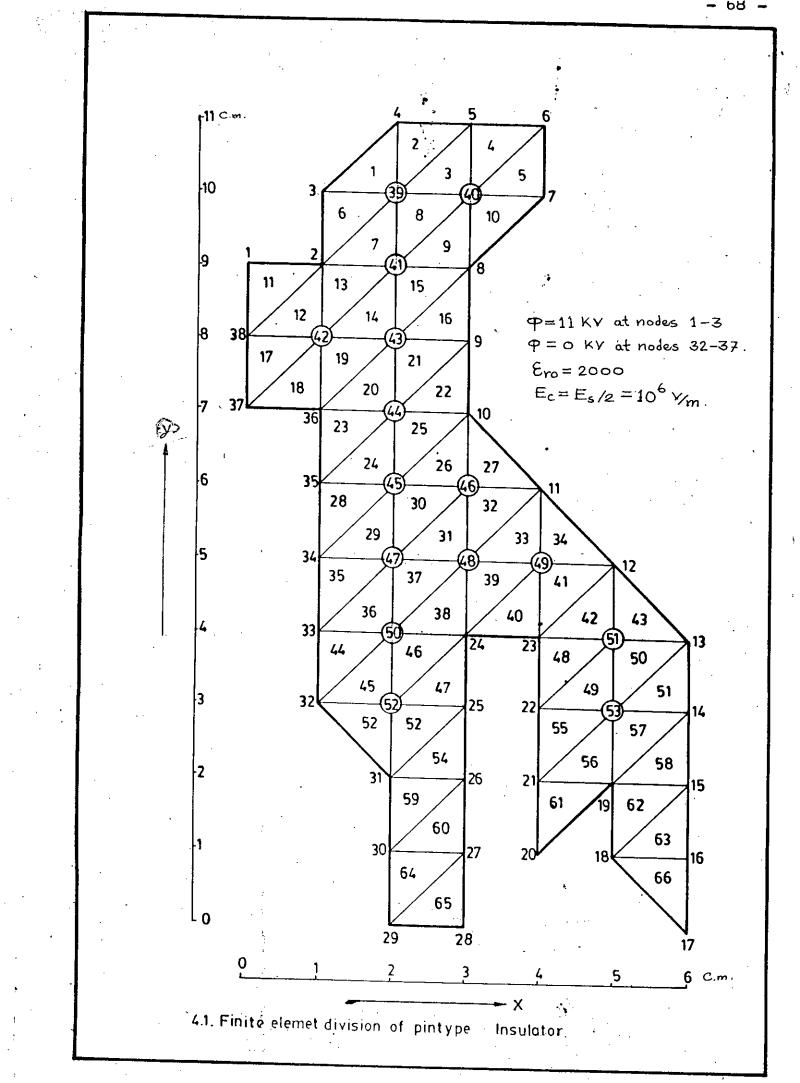
- Selection of high quality materials
- High manufacturing technique
- Strict quality control
- Suitable design engineering

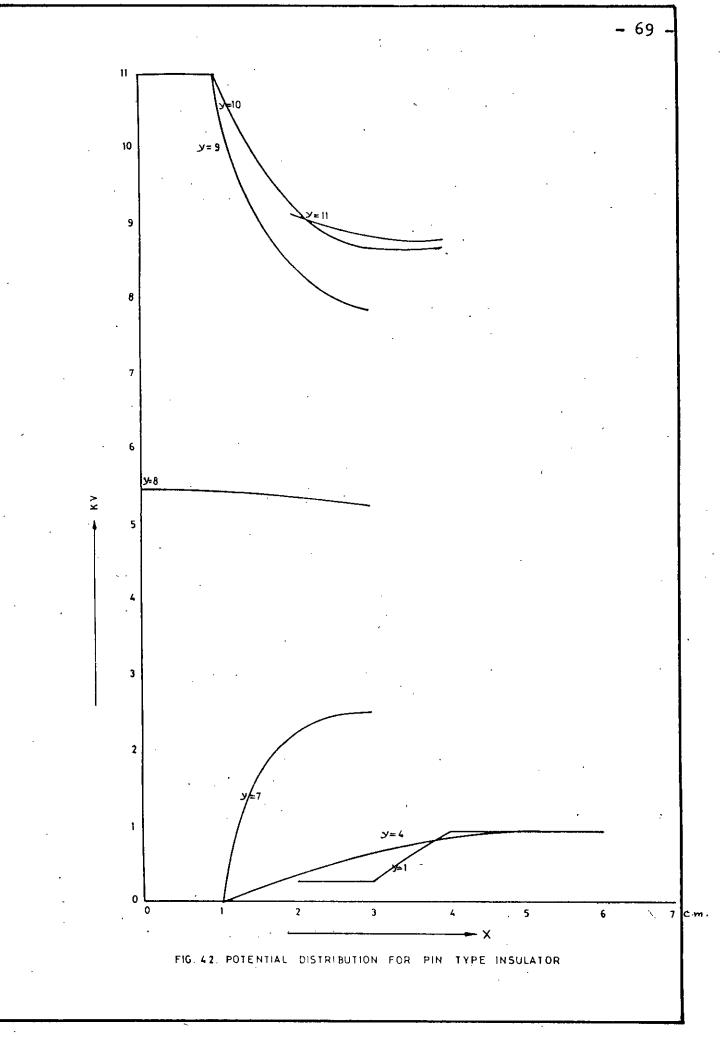
The mechanical strength of porcelain depends upon its raw material. So, the raw material must be free of ferrous perticles, the size and pores should be less and the amount of crystal should be more. Then using high manufacturing technique and strict quality control we can produce good quality of insulators with the application of suitable engineering design. The electro-mechanical stress analysis of ferro-electric material gives an idea about the stress distribution, magnitude of peak stress and angle of action.

4.2 Finite Element Design of a Pin-Type Insulator:

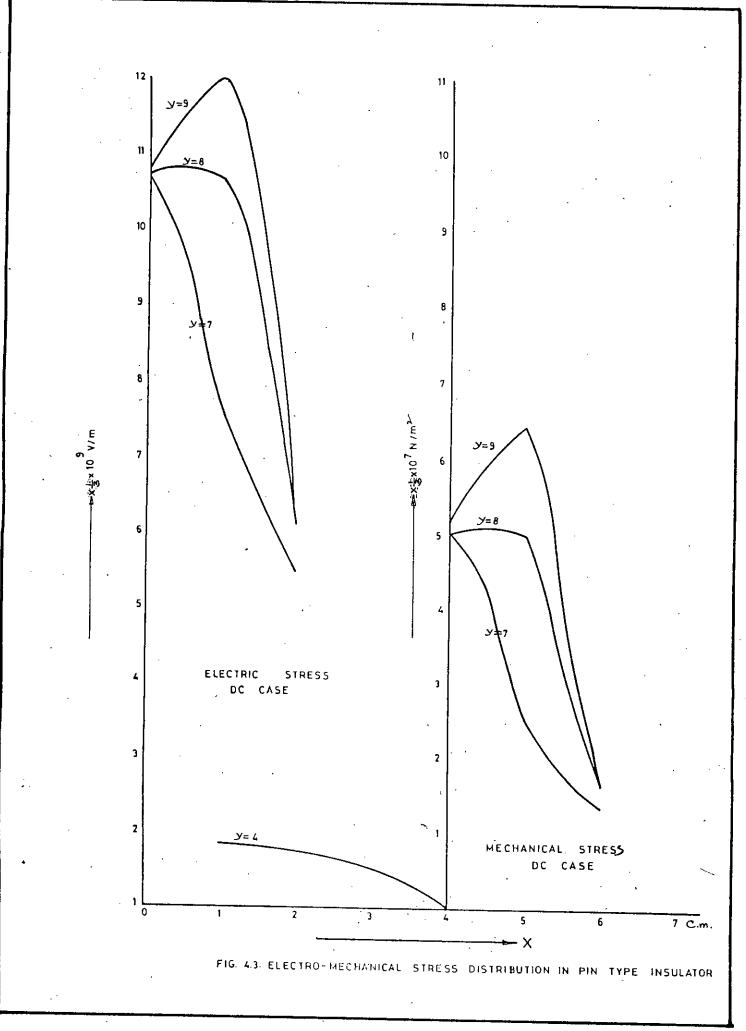
Pin type insulators are used in distribution lines for voltage ranges upto 33 kV. It is usually a one-piece construction and fitted with pin to the tower. The finite element design of this type of insulator can be performed using the electromechanical stress analysis for ferro-electric materials studied in chapter 3.

The pin-type insulator is symetrical about its axis. So we take half portion of it divided into 66 nos. of triangular elements as in fig. 4.1. The 66 no. of elements produces 53 nodes. Then taking 11 kV at nodes 1,2 and 3 and considering the pin at nodes 33-37 and applying the analysis of article 3.4 we get electric stress and equivalent mechanical stress distribution for static and alternating cases. The distributions are plotted in figs. 4.2-4.5.

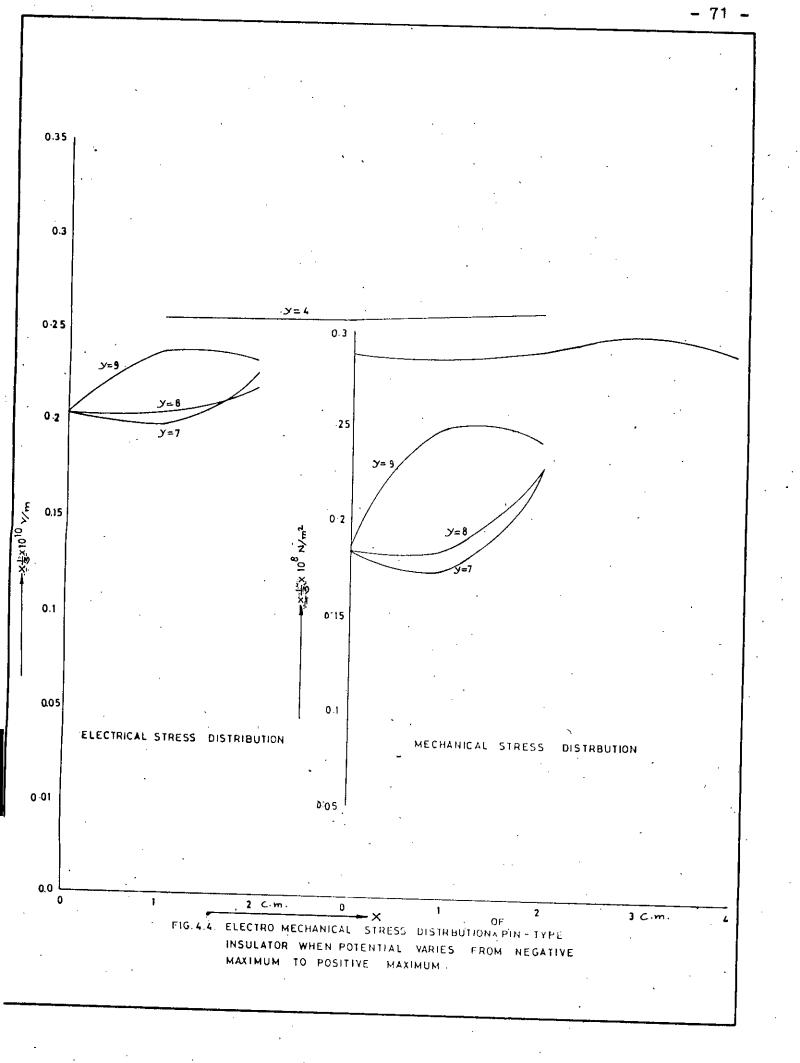




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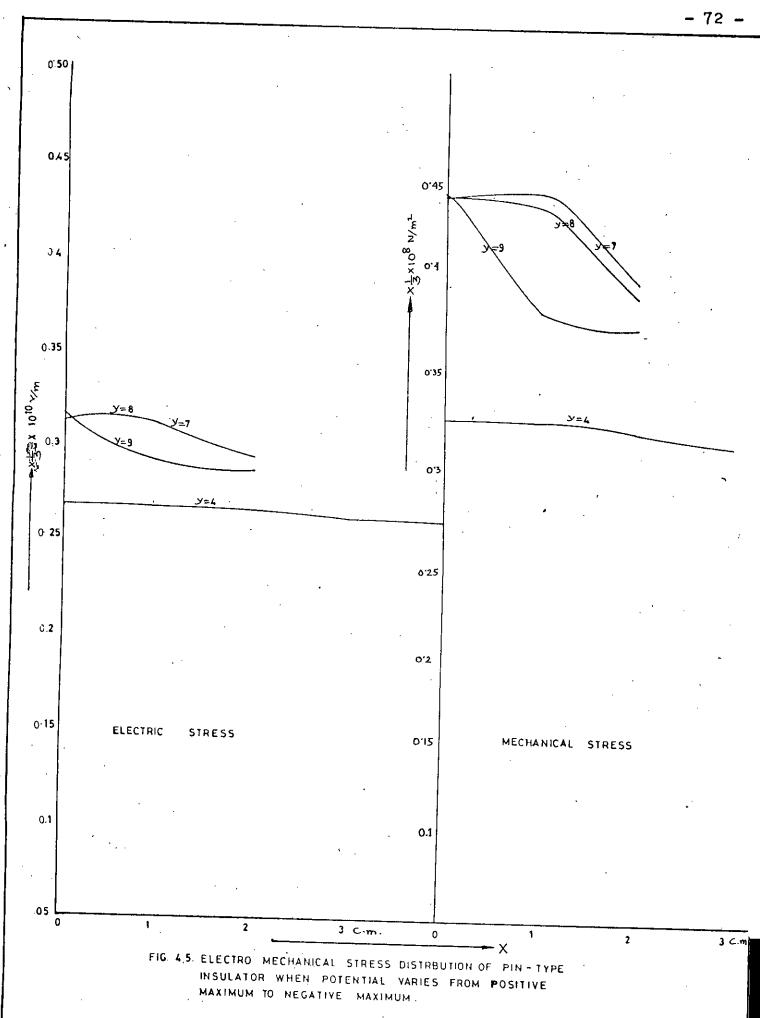


TABLE 4.1

Table showing average vertical stresses at different regions of the Pin-Type insulator considered in Fig. 4.1

4 3 2 1

	4 ,	•		
Region	Type of field applied	······		
considered	i ive of freid applied	Working Load	Average	Type of Stres
· · ·		(KN)	¦Stress in	1
	3	•	-Y-directio	חכ
	•	í , ···	¦ (KN/m²)	1
Top		¦		
Top region,	DC	- 0.54	1 -34.39	¦ Compressive
(elements	AC (negative maximum to positive	-12.20	-776.95	Compressive
1 - 10)	i maximum)	Ł	!	, compressive
	AC (positive maximum to negative	12.02	765.48	' ¦ Tensile
,	i maximum)	:	1 700.40	; (ensile
~~~ <u>~</u>	·	•		1 5 1
Between	l DC	8.75	1	· _ ·
Conductor	AC (negative maximum to positive	-28.53	3 744.24	l Tensile
and Pin	l maximum)	1 -20.JU 1	1-2524.77	Compressive
(elements -	AC (positive maximum to negative	34.79		
11 - 22)	. maximum)	1 34.77 I	3078.98	Tensile
		· · · · · · · · · · · · · · · · · · ·	i 	· · · · · · · · · · · · · · · · · · ·
Body region	DC	) 1	i	······································
(elements		-0.035	-1.14	L Compressive
28 - 43)	AC (negative maximum to positive maximum)	-1.414	-46.00	Compressive
- •=•			1	1
1	AC (positive maximum to negative maximum)	1.414	45.67	Tensile
·			1	1
uter Skirt ¦				······································
-	DC	0.00003`	-0.0005	Compressive
elements ;	AC (negative maximum to positive)	0.071	1.18	Tensile
55 - 66)	maximum)			i ienstie -
	AC (positive maximum to negative)	-0.071	-1.18	
1 1	maximum)		·	Compressive

Ł 22 4.-- **t** 

From the figures and numerical results we observe that the potentials of the nodes decreases as its distance increases from the potential plate and becomes zero at the pin i.e. at the ground plate.

From study of the average vertical component of stresses at different regions of the insulator as shown in Table 4.1, the following phenomena are observed:

(i) For d.c., the material between the pin and the conductor is subjected to a tensile stress and the remaining portion undergoes compressive stress. However, the insulator as whole is subjected to tensile stress.

(ii) For a.c. when the cycle varies from negative maximum to positive maximum the material above the pin undergoes compressive stress and the remaining portion undergoes tensile stress, but as a whole the insulator is subjected to compressive stress.

(iii) For a.c. when the cycle varies from positive maximum to negative maximum, the material above the pin undergoes tensile stress and the remaining portion undergoes compressive stress but as a whole the insulator is subjected to tensile stress.

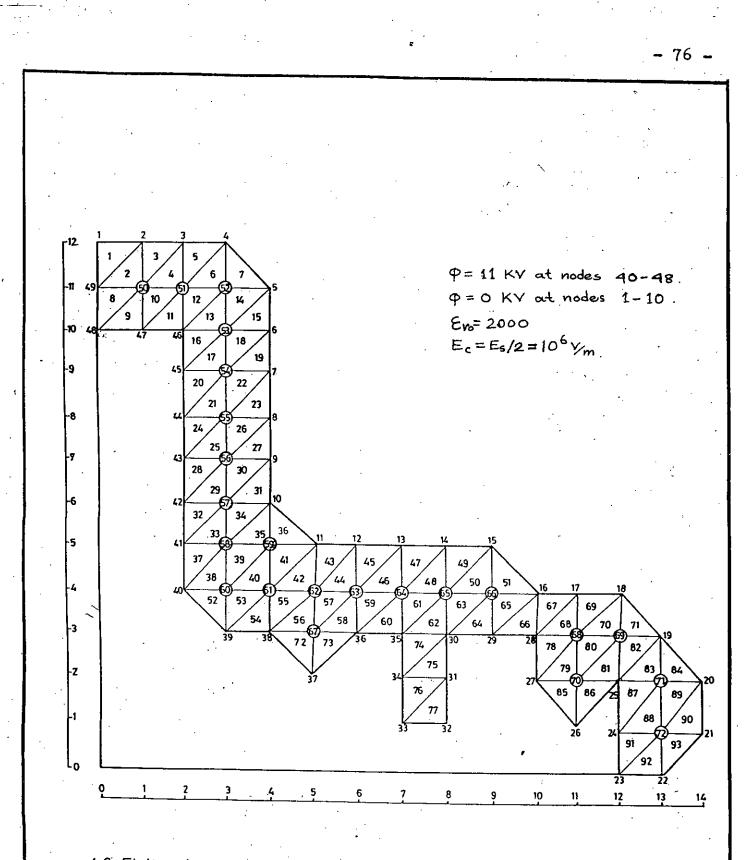
In all cases the average lateral component of stress is very high compared to the vertical component. It is tensile in nature and of the order of  $10^7$  N/m². However, for the proposed design the magnitude of electromechanical stress is greatly reduced compared with the case of hypothetically infinite lateral extent of the material as discussed in Chapter 3.

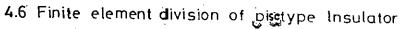
- 74 -

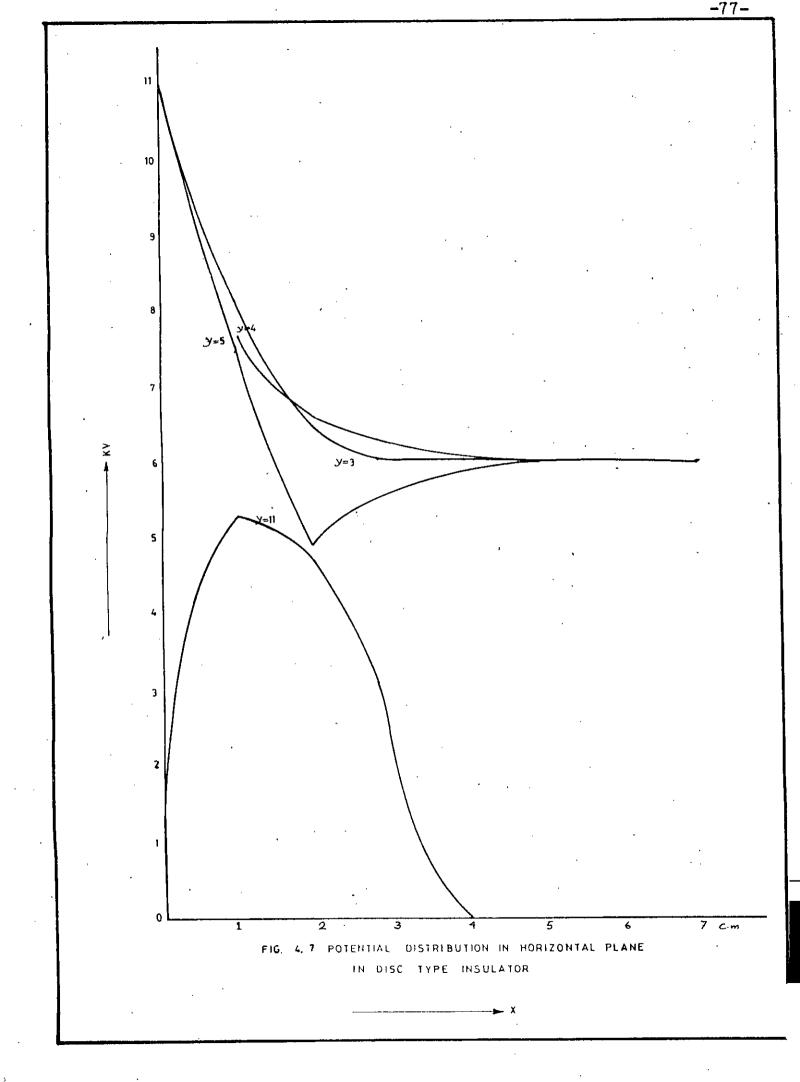
# 4.3 Finite Element Design of a Disc type Insulator:

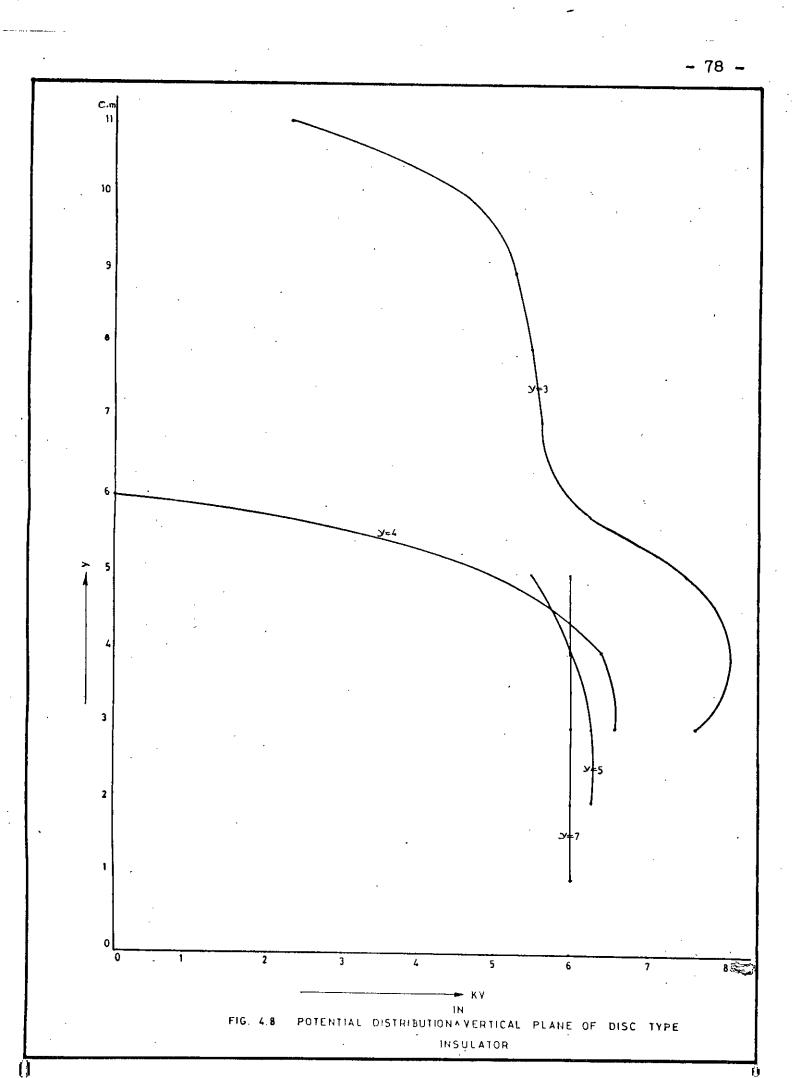
Disc type insulators are used The in constructing HV transmission lines. Usually this type of insulators are designed at a lower voltage say 11 kV and used as string for HV (132KV, 230KV, 400KV etc) transmission lines. The finite element design this type of insulator is performed applying the electroof mechanical stress analysis for ferro-electric materials in chapter 3. In doing so, the axially symmetric insulator is divided into 93 numbers of triangular elements as shown in fig. 4.6 which results 72 nos. of nodes. As the cap of the insulator remains at ground potential, we take the potentials of the nodes 1 to 10 as zero. As the conductor hangs with a steel pin fitted inside the insulator, we take 11 kV at the nodes 40 to 48 considering that each disc is designed for 11 kV). Now, applying the method developed in section 3.4 we get the distributions of electric and equivalent mechanical stresses developed within the insulator. The distributions are plotted in figs. 4.7-4.12.

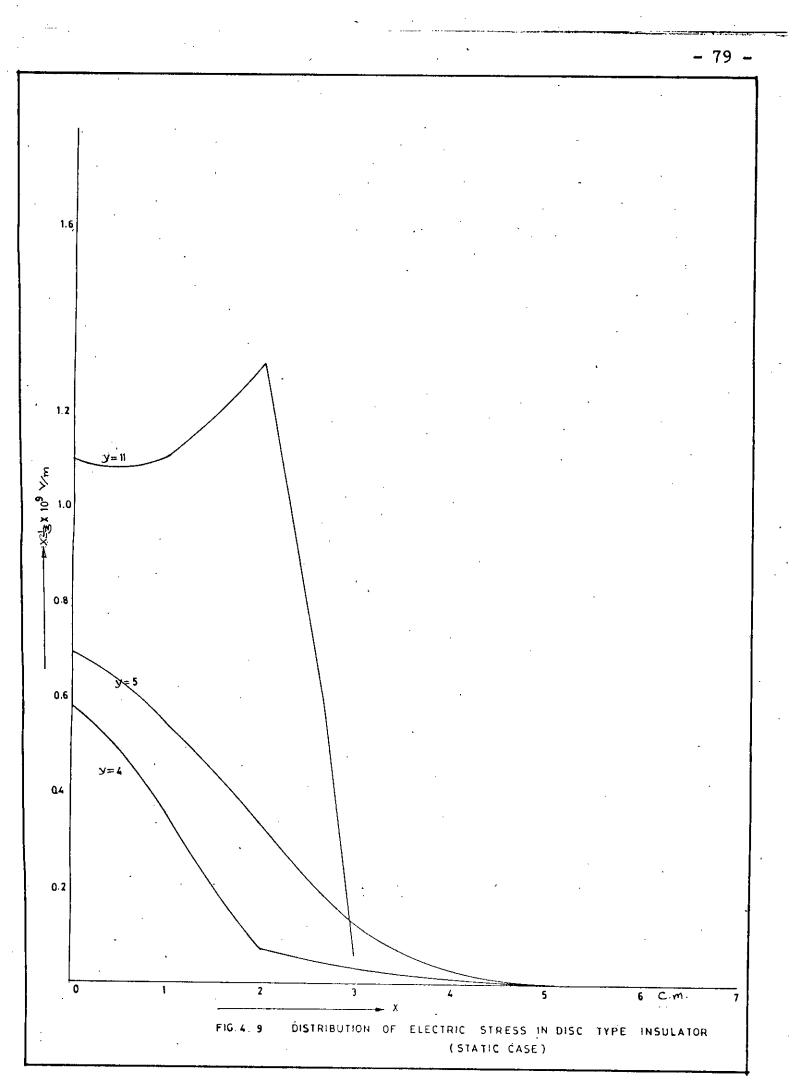
From the figures and numerical results we found that the potentials of the nodes decreases as the distance from the pin increases and becomes zero at the cap.

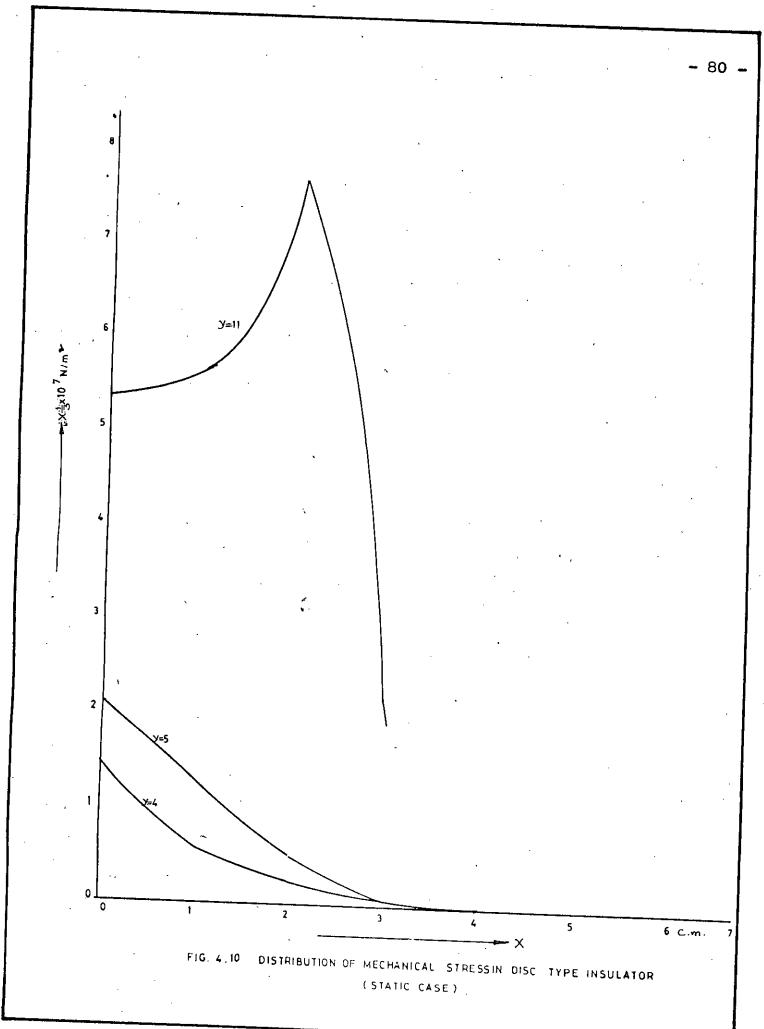




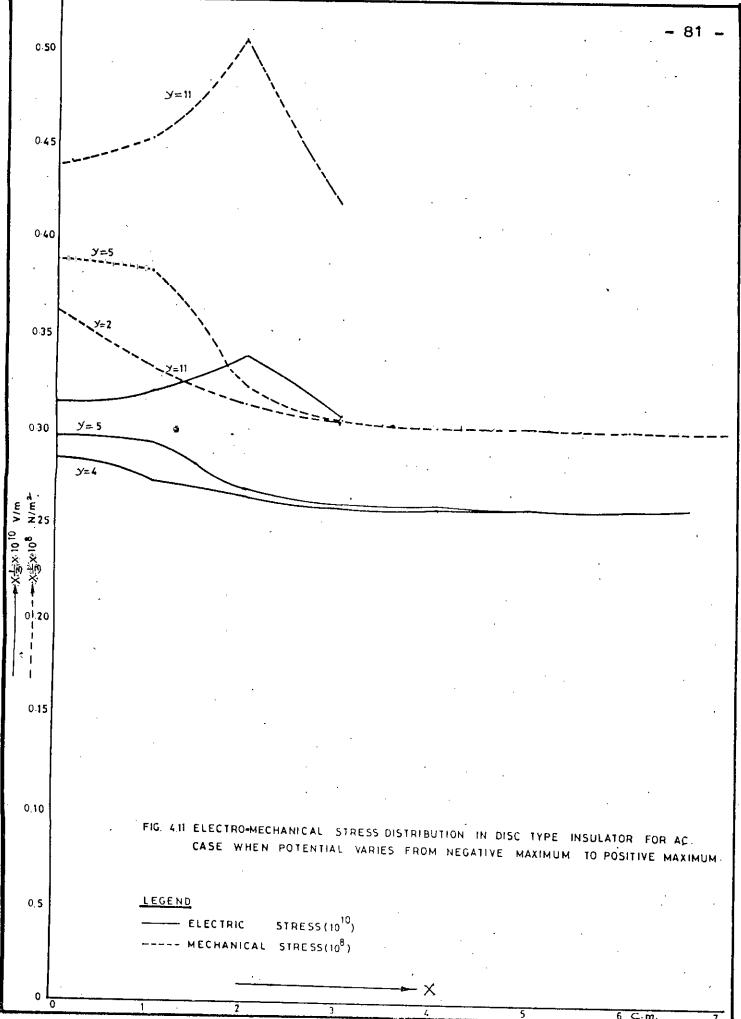








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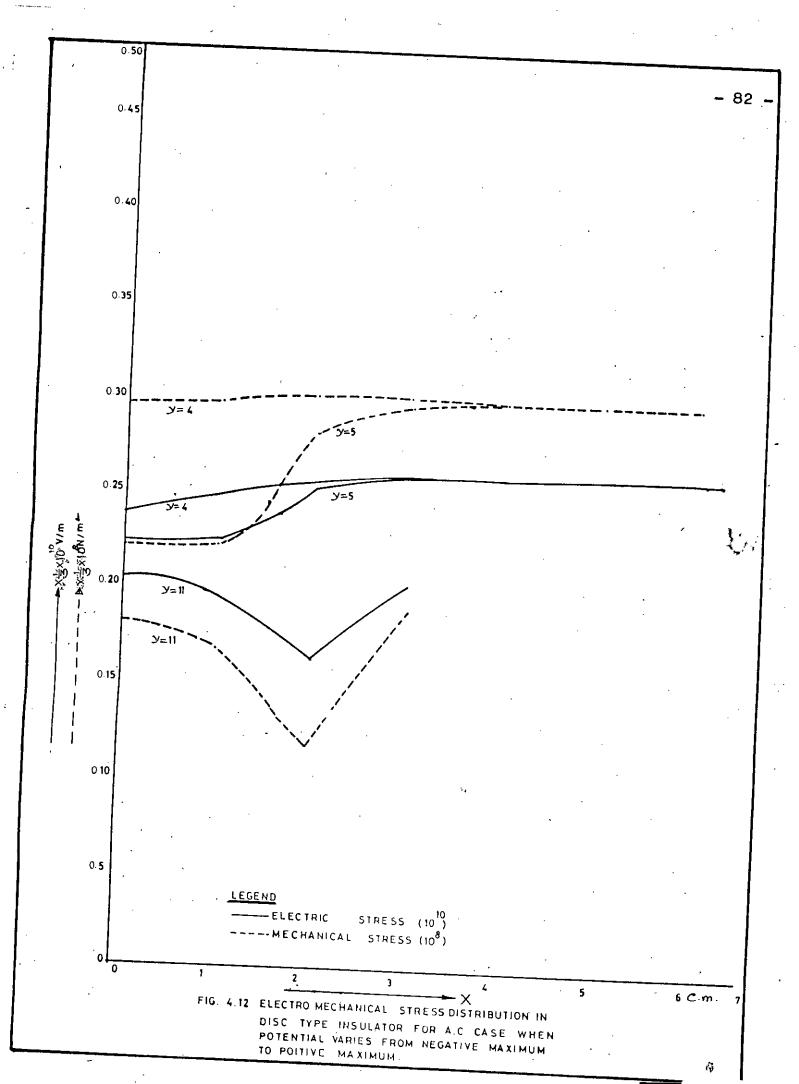


Table showing average vertical stresses at different regions of the Disc-type insulator considered in Fig. 4.6

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From the study of the average vertical component stress at different regions of the insulator as shown in Table 4.2. the following phenomena are observed:

(i) For d.c. the material of the top circular portion undergoes compressive stress and the remaining portion undergoes tensile stress. However, the insulator as a whole undergoes tensile stress.

(ii) For a.c. when the cycle varies from negative maximum to positive maximum, the material of the top circular portion undergoes compressive stress and the remaining portion undergoes tensile stress. However, the insulator as a whole undergoes tensile stress.

(iii) For a.c. when the cycle varies from positive maximum to negative maximum, the material of the top circular portion undergoes tensile stress and the remaining portion undergoes compressive stress. However, the insulator as a whole undergoes compressive stress.

In all cases the average lateral component of stress is very high compared to the vertical component. It is tensile in nature and is of the order of  $10^7 \text{ N/m}^2$ . However, for the proposed design the magnitude of electromechanical stress is greatly reduced compared with the case of hypothetically infinite lateral extent of the material as discussed in Chapter 3.

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#### 4.4 Discussion:

The design obtained in this section for pin type and disc type insulators are performed on the basis of finite numbers of elements and by analyzing the electromechanical stress for ferroelectric materials filling those elements. From the Table 4.1. and 4.2. it can be observed that the portion of the insulator which remains in contact with the conductor undergoes the maximum stress. Moreover, for a.c. the insulator is subjected to alternate compressive and tensile stresses with the alternation of cycle.

To check the validity of the present calculation we made a comparison with the electromechanical test data of disc-type insulator carried out by Swedish State Power Board materials Laboratory [19], when the insulator is subjected to 60 KV A.C. the observed average electromechanical load is 105.5 KN. According to the present calculation the average electromechanical load at 60 KV becomes 119.52 KN. This agrees reasonably well with the test result. It may be Mentioned that the difference in the working load is due to the value of internal field constant which we take 1/3 for BaTiO $_{\rm S}$  and this value may perhaps be slightly different.

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#### CHAPTER 5

# GENERAL DISCUSSION AND SUGGESTION FOR FUTURE WORKS

#### GENERAL DISCUSSION AND SUGGESTION FOR FUTURE WORK

Computer Aided design of ferro-electric insulators is carried over by calculating the electromechanical stress distribution in ferro-electric material by finite element method. Firstly, a Computer Program has been developed for calculating the electromechanical stress distribution in ferro-electric material of infinite extent and then it is modified to calculate the electromechanical stress distribution for the ferro-electric insulator of finite size.

To get an idea about the electromechanical stress over a region, it is first necessary to know the potential distribution over the region. The space between two circular parallel plates has been divided into a finite number of triangular elements. Then assuming linear dependence of potential over the elements Laplace's equation has been solved to get potential at different nodes. It is observed that for dielectric between two circular parallel plates, the potentials at different nodes converge to half of the applied potential at the midlevel between the parallel plates as the distance from the axis of parallel plates increases. The potential distribution has been plotted in Fig. 3.3.

Since ferro-electric materials are extensively used in fabrication of high voltage insulators because of their high relative permittivity, a study has been given to the electromechanical stress distribution in such materials in section 3.3. and 3.4. Because of the non-linearity in the medium, the stresses cannot be calculated in a direct manner. The finite element method enables us to linearize the medium in a piecewise manner and evaluate the effective non-linear characteristics. In view of the hysteresis curve of polarization of ferro-electric materials, three cases were investigated. These are 1-

- insulator subjected to d.c. voltage
- (2) insulator subjected to a.c. voltage and the applied voltage goes from negative maximum to positive maximum, and
- (3) insulator subjected to a.c. voltage and the applied voltage goes from the positive maximum to negative maximum.

The magnitude of the electric and equivalent mechanical stresses for the above three cases for material of infinite extent are plotted in Figs. 3.4, 3.5, 3.6, 3.7, 3.8 and 3.9 respectively.

For static case (Figs. 3.4-3.5) the peak stress occurs at the edge of the plate and the stress value drops rapidly for distance away from the edge. From the angle distribution shown in table 3.2, it is clear that half of the ferro-electric material experiences compressive stresses and the rest half experiences tensile stresses.

For alternating current when potential goes from negative maximum to positive maximum, the maximum stress occurs at the upper plate and the minimum stress occurs at the lower plate (Figs. 3.6 and 3.7). The stress curves attain a constant value as the distance increases from the axis of the plates. From the angle distribution (Table 3.3) it is clear that the material in between the plates is subjected to laterally expanding stress.

For alternating current, when potential goes from positive maximum to negative maximum, the maximum stress occurs at the edge of the lower plate and minimum stress at the upper plate (Figs. 3.8 and 3.9). The stress curves attain a constant value with the increase in distance from the plate. From the angle distribution (Table 3.4), it is clear that the material is subjected to laterally expanding stress. The greatest peak stress occurs in this case at the bottom plate. The electromechanical stress analysis for ferro-electric material of infinite extent developed in chapter 3 is applied for designing ferro-electric insulators of finite size. In doing so, we divided the insulator region into a finite number of elements (Figs 4.1 and 4.6) and applying the above analysis we get the results discussed below:

the design of pin-type insulator (Fig. For 4.1) the insulator region is divided into 66 numbers of elements comprising 53 nodes. The width of each elelment is taken as 1 cm. The potentials of different nodes decreases as its distance increases from the conductor and becomes zero at the pin. For d.c., the material between the pin and the conductor undergoes tensile stress and the remaining portion undergoes compressive stress. However, the insulator as a whole is subjected to compressive stress. For a.c. when the cycle varies from negative maximum to positive maximum, the material above the pin undergoes compressive stress and the remaining portion undergoes tensile stress. However, the insulator as a whole is subjected to compressive stress. For a.c. when the cycle varies from positive maximum to negative maximum, the materials above the pin undergoes tensile stress and the remaining portion undergoes compressive stress. However, the insulator as a whole iв subjected to compressive stress.

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the design of Disc-type insulator (4.6), the insulator For region is divided in 93 numbers of elements comprising 72 nodes. The width of each element is taken as 1 cm. The potentials at different nodes decreases as the distance from the pin increases and becomes zero at the cap. For d.c., the material of the top circular portion undergoes compressive stress and the remaining portion undergoes tensile stress. However, the insulator as a whole is subjected to tensile stress. For a.c. when the potential varies from negative maximum to positive maximum, the material in the top circular region undergoes compressive stress and the remaining undergoes tensile stress. However, portion the insulator as a whole is subjected to tensile stress. For a.c. when the cycle varies from positive maximum to negative maximum, the material in the top circular portion undergoes tensile stress and the remaining portion undergoes compressive stress. However, the insulator as a whole is wubjected to compressive stress. Therefore, the insulator is subjected to alternate compressive and tensile stresses with the alternation of cycle.

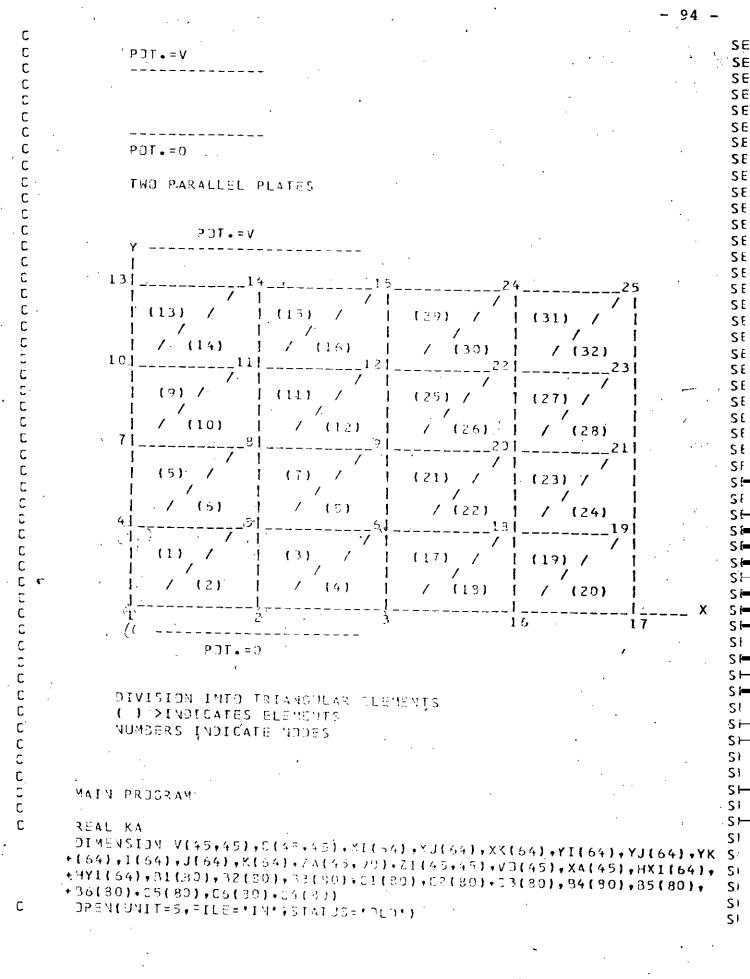
An interesting feature is that a severe lateral component of the electromechanical stress can be observed in the two ferro-lectric insulators designed in the present work. It is of the order of  $10^7 \text{ N/m}^2$  for a.c. and  $10^4 \text{ N/m}^2$  for d.c. with an 11 KV applied potential. Such lateral phenomenon seems to have not been studied extensively in experimental design of ferro-electric insulators. The finite element design of pin-type and Disc-type insulator performed in this thesis can be a very useful technique for designing ferro-electric insulators. Hence the analysis may be extended to get optimum design of ferro-electric insulators.

The electrothermal stress analysis and frequency response of insulators may be subjects of further research.

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FILE: SECHAR - FORTRAN AL BUET COMPUTER CENTRE: DHAKA



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95 DPEN(UNIT=3,FILE=*DUT*,STATUS=*NEW*)  $V \supset \{1\} = 0 \cdot 0$ S V9(2)=0.0S VU(3)=0.0 ς V3(13)=11000.0 S V3(14)=11000.0 V0(15)=0.0 DD 8 MV=4,12 V0(MV)=0.0 8 CONTINUE 00 71 45=15,45  $V_{0}(45) = 0.0$ 71 CONTINUE २ = 1 MML = 64 NON=45 DD 10 I4=1, VDV DD 10 JA=1.NDN V(TA, JA) = 0.010 CONTINUE DATA 1/4,2,5,3,7,5,3,5,10,2,11,9,13,11,14,12,5,3,16,15,9,6,20,18,15 +2,9,22,20,15,12,24,22,19,17,30,25,31,27,32,28,21,19,34,30,35,31,365 +,32,23,21,38,34,39,35,40,35,25,23,42,38,43,39,44,40/ DATA J/1,5,2,6,4,8,5,7,7,11,8,12,10,14,11,15,3,16,19,17,6,18,18,19 +,9,20,20,21,12,22,22,23,17,25,25,27,27,28,28,29,19,30,30,31,31,32,5 +32,33,21,34,34,35,35,36,30,37,23,38,38,39,39,40,40,41/ DATA K/5+1+5+2+3+4+9+5+11+7+12+8+14+10+15+11+18+18+18+19+20+20+21+5 +21,22,22,23,23,24,24,25,25,30,30,31,31,32,32,33,33,34,34,35,35,36,5 +35,37,37,38,38,39,39,40,40,41,41,42,42,43,43,44,44,45,45/ DATA XI/0.0,1.0,1.0,2.0,0.1.0,1.0,1.0,2.0,0.0,1.0,1.0,2.0,0.0,1.0,1.0,1.0 +,3.),4.),4.0,5.0,5.0,5.0,5.0,0.0,7.0,7.0,4.0,4.0,5.0,5.0,5.0,6.0,6.0,7.0,7. +.0,4.0,5.0,5.0,5.0,5.0,5.0,7.0,4.0,4.0,5.0,5.0,6.0,6.0,7.0,7.0 +/ JATA XJ/0.0,1.0,1.0,2.0,0,1.0,1.0,1.0,2.0,0,0,1.0,1.0,2.0,0,0,1.0,1 +.0+2.0,2.0,3.0,4.0,4.0+2.0+3.0,4.0+2.0,3.0,4.0,2.0,3.0,3.0,4.0,2.0,3.0,4.0,2.0,3.0,3.0 +,4.3,4.9,5.3,5.3,6.0,5.0,7.0,7.0,3.0,4.0,5.3,5.0,5.0,5.0,7.0,7.0,8 +.0,4.0,5.0,5.0,5.0,5.0,5.0,7.0,7.0,9.0,4.0,5.0,5.0,5.0,5.0,5.0,7.0,7.0,8.0 +/ +,4.0,5.0,5.0,5.0,5.0,7.0,7.0.3.0.5.0.5.0,5.0,5.0,5.0,5.0,7.0,7.0,8.0,8 +.0,5.0,5.0,5.0,5.0,7.0,7.0,8.0,8.0,5.0,5.0,5.0,5.0,7.0,7.0,8.0,8.0 +/ DATA YI/1.0,0.0,1.0,0.0,0.0,0.1.0,1.0,2.0,1.0,3.0,2.0,3.0,2.0,4.0,3.0,4 +.0,3.0,1.0,J.0,0.0,0.0,2.0,1.0,2.0,1.0,3.0,2.0,3.0,2.0,4.0,3.0,4.0 +,3.0,1.0,0.0,1.0,0.0,1.0,).0,1.0,0.0,2.0,1.0,2.0,1.0,2.0,1.0,2.0,1.0,2.0,1 +.0,3.0,2.0,3.0,2.0,3.0,2.0,3.0,2.0,3.0,2.0,3.0,4.0,3.0,4.0,3.0,4.0,3.0,4.0,3.0 +/ DATA YJ/D.0,1.0,0.0,1.0,1.0,1.0,1.0,2.0.2.0,3.0,2.0,3.0,3.0,3.0,4.0,3 +.0,+.0,0.0,0.0,1.0,0.0,1.0,1.0,1.0,1.0,1.0,2.0,2.0,2.0,2.0,2.0,3.0,3.0,3.0 +/

FILE	SEKHAR	FORTRAN	AL BUET	COMPUTER	CENTRE+ D	DHAKA	n	
		()				,		96. –
· · · · ·	JAIA YK/	/1.0,0.0,1.	0,0.0,2.0	0+1+0+2+0	,1.0,3.0,2	2.0.3.0.	2.0,4.0	+3=0+4
	++++0+1+0	$1 \cdot 0 \cdot 1 \cdot 0 \cdot 1 \cdot 0$	J#I+J+ <u>Z</u> +J	• Z • J • Z • J •	2+0+3+0+3+	0+3+0+3	-0+4+0+	4.0.4.
÷	+.0,3.0,	0+1•0+1•0+ 3•0+3•0+3•0	D•3•3•3•3	• 3 • 3 • 3 • 9 • 1	0,2	2 • 0 • 2 • 0	+2+0+2+	0,2.0,
	•			• • • • • • • • • • • • •	4004400446	•U+4+J+4	•0•4•0•	4.0,4.
	WRITE(3)					•		*
. 11	FORMAT(4	X, "ELEMENT	TS OF MATE	RIX•/)			- ark	
	DD 20 JJ DD 30 II						alt i i	
••	DO 30 J	J= L • N J N ] = ] • N J N					•	
· · ·		=0.0						en a la regió
· 30 [·]	CONTINUE						• •	• • E
	XI1=XI(J					· •	·~ • · ·	· .
• •	XJI=XJ(J		-				:	
	XK1=XK[J YI1=YI[J						•	
· · ·	YJ1=YJ(J							• • • •
• •	YK1 = YK ( J							. ·
•	I1=I(JJ)	-						<b>.</b>
•	'15=1(11)						×	
	<1=K(JJ)						•	•
	BI=YJ1-Y BJ=YX1-Y					- 1	•	1 - 1 - 1 - 1
ant i	BJ-781-9 BK=711-7							
	C1=X<1-X					•		
Ŧ	CJ=X11-X							
	CK=XJ1-X					•		
•	2(11,11)	=[81481+C1	\$CI}\$R				ł	
	- C(J1,J1)	=(BJ*BJ+CJ	J∜CJ] %R			•	н 	÷
•		=(BK≑BK+CK =(BI≿BJ+CI				۰۰ ب سو		÷ •
· · · ·	' C(I1.K1)	=(BI*8J+CI =(BI*8K+CI	- ヤレリノネス 			1 	· · · · · · · · · · · · · · · · · · ·	•
	C(J1,K1)	=(BJ*BK+CJ	I¢CK1¢R			<u>}</u> 4	そう 月間	
	-C(J1,I1)	=C(I1,J1)						
	2(<1+J1)	=C[J1,K1]						· · · · ·
r	-((I,II)	=C(I1,KI)				. :	.'	- ⁻ -
	VI 52 GC	=1.2000				· •	· · · ·	,
- 1	VL 22 CC		<u> </u>				•	· ``
	VIIV,JV)	=V(IV,JV)+	C(IN.IN)					
. 22	CONTINUE							
. 20	SUNITACS					• •	•	•
r	00 17 I?	=1,2					· .	
÷	DD 17 JP V(IP+JP)					•	·	
1.7	CONTINUE						•	•
	00 18 10						- ,	- /
	DO 18 JQ	=1+NON				-		
•.	([2,12)							
18	CONTINUE			•		•		· · · · · · · · · · · · · · · · · · ·
	00 19 IX					•		
. 19	V(IR,IR) CONTINUE					, r	· ···	
. 17	V(13,13)							
	V(14+14)	=1.0				-	•	•
			•			• •		
		·					• • •	
•						•		r sreen
								din e

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# FILE: SEXTAR FORTRAN AL BUET COMPUTER CENTRE, DHAKA

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· 3'		-
	WRITE(3,95)	SEK
. 95		SE
C	SCHITTERY (SOB 42X4 FORENTIAL AT BIFF (UDE(V)*/)	SE
-	DD 29 IJ=1,NDN	SEF
		S E I
	DD 29 JI=1,NOM	SEF
	ZA(IJ,JI)=V(IJ,JI)	SE
29		SE
CSOL	JTION OF MATRIX TO FIND POTENTIALS	
C		SE)
_		SE
	CALL INVERT(ZA,45,ZI)	SE
	CALL MATV(ZI,VO,XA,45)	SEX
	DO 21 MA=1, NON	SE
	WRITE(3,26)MA,XA(MA)	SE
26		
21	CONTINUE	SEF
с·	Continue .	SE
		SEK
С	ARITE(3,138)	SE*
	PI=3.141592654	SE
	ED=+0000000008854	
	ES=2000000.	SEX
	EC=1000000.	SE
		SE
	CJ2=3+0*(ES**2)+EC**2	SEX
	CO3=1.0/CO2	SEk
	CO=CO3	SEX
	ERD=2000+0	
	√0=ER0*CD	SEK
с		SEX
ς.		SEX
	DO 37 M=1,NML	SEK
	XI2=XI(M)	SEK
	XJ2=XJ(M)	
•	XK2=XK(M)	SEX
•	YI2=YI(Y)	SEX
•	YJ2=YJ(Y)	SEK
•		SEX
	YK2=YK(M)	SEK
	B1(M) = YJ2 - YK2	SEK
	B2(Y) = YK2 - YI2	
	B3(Y) = YI2 - YJ2	SEK
		SEX
	C1(Y) = X(2 - XJ2)	SEK
	C2(4)=XI2-XK2	SEK
	C3(M) = XJ2 - XI2	SEK
5		
	L1=I(M)	SEK
		Sek
	LZ = J(M)	SEK
•	L3=<(M)	SEX
	EX0=-(B1(M)*XA(L1)+B2(M)*XA(L2)+B3(M)*XA(L3))*100.0	SEK
	EYD=-(C1(M)*XA(L1)+C2(M)*XA(L2)+C3(M)*XA(L3))*100.0	
C	EZO=SQRT(EXO**2+EYO**2)	SEX
-		SEK
	DX1=E0*(ER0*EX0-W0*EX0**3)	SEK
	DY1=E0*(ER0*EY0~W0*EY0**3)	SEK
	Exl=(((ERD-1.0)/3.0)+1.0)*EX0 -(WD/3.0)*EX0**3	SEK
	EY1=(((ER3-1.0)/3.0)+1.0)*EY0-(W3/3.0)*EY0**3	
	EZ1=SQRT(EX1*EX1+EY1*EY1)	SEK
		SEK
r		6 -14
C	TY1 = (DY1 + EY1 - DX1 + EX1)/2.0	SEK
C C	$TX1 = SQRT(EX1 \neq EY1 \neq DX1 \neq EY1)$	SEK

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### FILE: SEKHAR , FORTRAN AL BUET COMPUTER CENTRE, DHAKA

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			:0
С	$TT1 = SQRT(TX1 \neq 2 + TY1 \neq -2)$	· .	SEK(D
C	S3=1000000+0		SEX()
	-		SEKIO
	S4=EXO+SB		SEKID
-	S5=EY0+S3		SEKIÓ
C	DX2=E0*(ER0*54-10*54**3)		
C	DY2=E04(ERD/S5-404S5+43)		SEK(0
	EZ2=SQRT(EX2*+2+EY2*+2)	, •	SEKto
	EA2=ATAN(EY2/FX2)*(130.0/PI)		SEK()
	EX2=(((ER0-1.0)/3.0)+1.0)#S4-(40/3.0)*S4**3		SEKto
,	EY2=(((ERU-1.0)/3.0)+1.0)~S5-(40/3.0)*S5**3		SEKVO
C	TY2=(DY2*EY2-DX2*EX2)*0.5		SEK()
C	TX2=SQRT(DX2^DY2AEX2(EY2))	•	SEK(a
C	TT2=SQRT(TX2402+TY2001)		SEK(0)
С	AN32=ATAN(TY2/TX2)((130-0/PI)	ι.	SEKIO
	56=EX0-3B		SEK(p
	S7=EY0-S3		SEKID
	DX3=ED%(ERD%S6-ND%S6%%3)		SEK(j
	DY3=EJ4(ERJ#S7-WO*S7443)		SEK(0
	EZ3=SQRT(EX3**2+EY3***2)	· ·	SEKKO
	EAB=ATA4(EY3/EX3)*(180.0/PI)	·	SEKIO
	EX3=(((ER0-1.0)/3.0)+1.0) ~So-(VD/3.0) ×So=3		SEKIO
	EY3=(((ER0-1.0)/3.0)+1.0)*\$7-(40/3.0)*\$7**3		SEKto
С	TY3=(DY3%EY3-DX34EX3)&9.5		SEKin
	FX3 = SQRT(QX3 + QY3 + EY3 + EX3)		SEKO
· C C ·	TT3 = SQRT(TX3 + 42 + TY3 + 42)		SEK (5
č	ANG3=AFAN(TY3/TX3)*(100+0/PI)		SEKIO
	IF(EX1.ED.0.) D41=-90.		SEK a
С	IF(EX1.2.0.)4NG1=90.	•	SEK 0
+	IF(EX1.E).0.)30 TO 200	•	SEK
	E41=ATAN(TY1/IX1)>(190.0/PT)		SEKto
•	IF(EX1.LT.D.) HAL=FA1-130.		SEKO
Ĉ.	ANG1=ATA'(TY1/TX1)'(180.0/PI)		SEKÄ
C200			SEKC
C132	- FURMAT(1X, T2, 1X, T10.4, 1X, F7.2, 1X, E10.4, 1X, F7.2	,1X,510.4.1X,F7.2/)	SEKO
C	IF(EX0.E0.0.)2A0=-70.		SE∢o
C	IF(FX0.E0.0.)00 TU 200	· · · ·	S≘Ko .
č	EAB=ATAN(EYD/EXD)*(100./PI)	· ·	SEKo
200	WRITE(3,132)M, EZ1, EA1, EZ2, EA2, EZ3, EA3	•	SEK()
	<pre>FURMAT(1X,I2,1X,F10.4,1X,F7.2,1X,E10.4.1Y,F7.6)</pre>	(.1X.E10.4.1X.E7.2/)	
c	+E10.4.2X,F3.2/)		SE<;
37	CONTINUE		SE<:0
C .			SEK:0
<b>.</b>	STOP		SEK.0
			SEKIO
С	SUBROUTINE TO OBTAIN INVERSE OF A MATPIX		SEK(0
-	SUBROUTINE INVERT(ZNANAZI)		SEKig
	DIMENSION ZA(45,90),ZI(45,45)		SEKIO
	M=N+N		SEKIO
	$\frac{1}{\sqrt{2}} = \sqrt{+1}$	·	SEKIO
	70 24 LI=1, N		SEX(0
			SEKIO
24	$ZA(LI_{2}LJ)=0.0$		SEKIO
<u>با</u>	DD = 81 + 4 = 1 + N		SEKIO
	$I2 = \langle +N \rangle$		SEKO
31	$ZA(\langle , I2 \rangle = 1.0$		SEKO
чж. -	μ. · · · · <b>γ</b> · · μ. <b>γ</b> · · μ. · · · · · · · · · · · · · · · ·		
	•		

FILE:	SECHAR FORTRAN AL BUET COMPUTER DENTRE,	ЭНАКА	
• • •			- 99 -
	ZA(LJ,I) = ZA(LJ,I)/P	۰. ۳	SEA:
L C 15	WRITE(3,15)ZA(LJ,I) Format(E10.4)		SEX
- 44	CONTINUE		SEX SEX
	DD 101 LK=1,N DD 101 LI=J2,M		SEX SEX
28	IF(LK-LJ)28,101,28		SEX SEX
101	ZA(LK,LI)=ZA(LK,LI)-ZA(LJ,LI)&ZA(LK,LJ) CONTINUE		SEX SEX
	)) 102 I=1,N 0) 102 J=M2,M	·	SE<
102	L3=J-N		SEK
102	ZI(I,L3)=ZA(I,J) RETURN		SEK
5 g. C	END SUBROUTINE TO MULTIPLY A MATRIX BY A VECTOR		SEK
•	SUBROUTINE MATV(ZI,VO,XA,N)		SEK SEK
· · · ·	DIMENSION ZI(45,45),XA(45),VO(45) N=45		SE<
·	)) 7 IH=1,V SJM=0.0		SEK SEK
	00 41 KH=1,N		SEK
<u>2</u> 41 9	·SUM=SUM+ZI(IH,KH)≈VD(KH) X4(IH)=SUM		SEC
	RETURN	•	SE¢ SE¢
	END		SEC
		· .	• 200
		. •	
4			
		•	)
u er F	· · · · · · · · · · · · · · · · · · ·		
в. 			· · · · · · · · · · · · · · · · · · ·
3 3 4		• *	
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FILE: SEKHAR OUTPUT AI	BUET COMPUTER CENTRE, DHAKA
TELECTROMECHANICAL STRESS	ANALYSIS DE FERROELECTRIC MATERIAL
NODE POTENTIAL AT DIFF ND	لائين معند مان من مشرق مين . مانيا
L 0.00	
2 0.00	
3 3204.12	
<b>4 2953</b> •16	
<b>5</b> 3156•38	اندې د د د چې د د د چې د د د د د د د د د د
6 4172.45	
7 5499.92	و مربقه المحمد المح المحمد المحمد المحمد المحمد المحمد
· · · · 8 5499•91	
9 5499.87	
10 8046.71	
· · ·	
11 7843.48	
12 5827.32	الله الجيرة أن منها بالم المراجع . منهم المراجع المراجع المراجع . مراجع المراجع المراجع .
13 11000.00	
14 11000.00	
15 7795.69	
16 4471.59	
- 17 5023.42	
· · · ·	-1
19 5173.80	
⁶⁹ 20 5499•84	: به معرف محمد محمد المحمد ال
21 5499.82	
22 6170-28	
23 5825.82	
24 5528.11	
25 5975-21	terretaria de la constante de l La constante de la constante de La constante de la constante de
26 5274.50	· · · · · · · · · · · · · · · · · · ·
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5389+45		
5439.00	$(x_1, x_2) \in \mathbb{R}^{n \times n}$	
5452.79		· · ·
5342.56		
5422.16		
5456.83		
5465.58	,	
5499.79		• •
5499.78	<b>、</b>	
5499.77		

 37
 5499.77

 38.
 5657.02

 39
 5577.39

 40
 5542.67

41 5532.97 42 5725.10 43 5610.11

44 5560.55

45 5546.76

	TT1	ANG1	TI2	ANG 2	TT3	ANG 3
1	<b>J.510</b> 8E+06	82.07	0.7579E+07	-16.48	0.1273E+08	10.48
2	3.5797E+05	90.00	0.+7507E+07	-18.90	0.1272E+08	12.03
3	0.6406E+05	54.08	0.6767E+07	-13.88	0•1358E+08	7.58
.4	0.5524E+05	-55.14	0.6773E+07	14.50	0.1358E+03	-7.92
5	J⇒3794E+05	90.00	0.8043E+07	-14.50	0.1222E+08	10.14
6	0.32425+06	80.05	0-3023E+07	-12-28	0.1222E+08	8.52
7	0.3218E+05	90.00	0.8193E+07	-13+24	0.1205E+08	\$ 9.47

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	3	0.16475+06	15.11	0+8140E+07	-1.75	0+1205E+08	1.26	
	9	9.3819E+06	80.83	0•8214E+07	-15.52	0.1205E+03	11.11	
	10	0.3213E+05	90.00	0.8193E+07	-13.24	0.1205E+08	9•47	
	11	0.3827E+05	42.97	0.9053E+07	-17.57	0.1121E+08	14.58	
	12	0.1038E+06	90.00	0.8980E+07	-6.97	0.1119E+08	5.76	
	13	0•5085E+06	90.00	0.7749E+07	-17+43	0.1256E+08	11.42	
	14	0•5322E+06	82.53	0.7777E+07	-19.80	0•1255E+08	12.99	
•	15	0+1177E+07	-3.85	0.1030E+08	-30.03	0.1J22E+03	30.23	
	16	0.1152E+06	-2.75	0+1013,E+08	-9•44	0+1005E+08	9.50	
	17	0.3081E+05	21.67	0.8723E+07	-1.57	0.1144E+08	1.32	
	18	0.1022€+06	-58.44	0.87292+07	4.38	0.1144E+08	-3.87	
	19	0.1457E+05	2.19	0.9483E+07	-0.07	0.10668+08	0.05	
•	201	0.1932E+05	-59.51	0.9434E+07	2.02	0.1066E+08	-1.82	
	21	0.1038E+05	90.00	0.89302+07	-6.97	0.1119E+08	5.76	
	22	0.5202E+05	1.16	0:8956E+07	-0.07	0.1119E+08	0+06	
	23	0.26548+05	. 90.00	0.9513E+07	-3.35	0.1064E+08	3.05	
	24	0.13298+05	-3.14	0.9510E+07	0.09	0.1063E+08	-0.03	
	25	0.1293E+06	37.29	0.9535E+07	-9.93	0•1065E+03	9.03	
	26	0.2554E+05	39.99	0.9513E+07	-3.36	0.1064E+08	3.05	
	27	0.3355E+05	35.60	0.98035+07	-4.95	0.10355+08	4.73	
	28	0.5279E+04	89.79	0.9797E+07	-1+59	0•1034E+08	1.52	
	27	0.1500E+06	-15.22	0.1034E+08	-10.44	0.9847E+07	10.90	
	30	0.3306E+05	-32.84	0.1033E+08	-4.74	0.9825E+07	4.95	
	31	0.2555E+05	-24.08	0•1024E+08	-4.28	0.9912E+07	4•40	
	32	0 <b>.</b> 8345E+04	42.82	0.1023E+08	-2.33	0•99082+07	2.40	
	33	9.3019E+04	-5.59	0.9803E+07	0•09	0.1034E+08	-0.09	
	34	0 <b>.</b> 3998E+04	-59.67	0.9803E+07	0.89	0.1034E+08.	-0-85	-
	35	0.6431E+03	-8.94	0.9946E+07	0.05	0.1019E+03	-0:05	

- 103 -

36	0.84408+03	-58+23	0•9946E+07	0+40	0.1019E+08	-0.39	
37	0.1344E+03	-3.40	0.1001E+08	0.01	Q:1013E+08	-0,01	
38	0.1639E+03	-50.32	0.1001E+08.	0415	0.1013E+08	-0-15	
39	0.2445E+02	. 33.02	0.1005E+08	-0.04	0.1009E+38	0•04	
40	<b>3.</b> 2248E+32	-0.02	0.10052+38	0.00	0+1009E+08	0.00	
41	0.52792+04	87.97	0•9797E+07	-1•59	0.1034E+08	1.52	
42	0.3143E+04.	-4+05	0•9797E+07	0+05	Ó+1034E+08	-0.05	
43	0*1461E+04	89.99	0+9738E+07	-0.76	0+1020E+08	0.74	
44	0.7303E+03.	·-1•45	0•9938E+07	0.01	0.1020E+08	-0.01	
45	0.3559E+03	89.99	0.10005+08	-0.37	0.1014E+08	0.37	•
46	0.1799E+03	12.03	0+1000E+08	-0*04	0+10145+08	0.04	
47	0.10378+03	90.00	0+1003E+08	-0.21	0+1011E+08	0 • 20	
48	0.7055E+02	57-41	0.1003E+08	-0.11	• 0•1011E+08	0.11	•
49	0.7952E+04	35+25	0•9939E+07	-2.39	0.1020E+08	2.34	
50	0.14613+04	89.93	0 <b>.</b> 9938E+07	-0.75	0.10202+08	0.74	
51	0.1835E+04	35.28	0.1001E+09	-1.14	0.1014E+08	1.12	
52	0 <b>.</b> 3550E+03	87.98	0.1000E+08 ;	-0.37	0.1014E+08	0.37	
53	0.42728+03	41.80	0.1003E+08	-0.54	0.1011E+08	0.53	
54	0.10375+03	189+93	0.1003E+08	-0.21	.0+1011E+08	0.20	
55	0.1143E+03	64.51	0.1004E+08	-0.25	0.10105+03	0.25	
56	0.6511E+02	90.00	0+1004E+08	-0+15	0.10105+08	0.16	
·57	0.50528+04	-28.15	0.1016E+08	-1.90	0•9986E+07	1.93	
58	0.1957E+04	-45.07	0.1015 E+ 08	-1.12	0.9986E+07	1.14	
- 59	0.10552+04	-28.75	0.1011E+08	-0.87	0.1003E+08.	0.83	
60	0.4379E+03	-45.33	0.1011E+08	-0.53	0.1003E+08	0.54	
<del>5</del> 1	0.2083E+03	-23,14	0-1003E+08	-0.39	0.1006E+08	0.39	
62	0.90135+02	-35.50	0.1008E+08	-0.25	0•1006E+08.	0.25	

F	ILE:	SEKHAR	OUTPUT	A1 BUET COMPUTER CENTRE, DHAKA	· ,
					- 194 -
	63 (	D•3014E+;	02 .14•71	0.1007E+08 -0.15 0.1007E+08	0•15
•				0.1007E+08 -0.11 0.1007E+08	0.11

TT1 Mechanical Stress (D.C. case) Mechanical Stress Angle (D.C. case) ANB1 TT2 Mechanical Stress (AC, negative maximum to positive. maximum Mechanical Stress Angle (AC, negative maximum to ANG2 positive maximum) TT3 Mechanical Stress (AC, positive maximum to negative กัสหม่านก Mechanical Stress Angle (AC, positive maximum to ANG3 negative maximum)

FILE: SEKHAR OUTPUT A1 BUET COMPUTER CENTRE, DHAKA

- 105 -

ELECTROMECHANICAL STRESS ANALYSIS OF FERROELECTRIC MATERIAL ELECTRICAL STRESS DISTRIBUTION

			RIDOTION		-			
=	Z 1	EA1	EZ2	EA2	EZ3	, EA3		
1 0.1	952E+09	-93.95	0.00005+00	0.00	0.0000E+00	000		
2 0.2	090E+09	-90.00	0.7558E+09	36.76	0.9795E+09	50.24		
3 0.2	197E+09	-107.95	0.7572E+09	35+55	0.9792E+09	51.02	,	
4 0.2	2172+09	-153.07	0.71425+09	38.05	0+1012E+10	48.79		;
5 0•1	691E+09	-90.00	0.71452+09	52.25	0+1012E+10	41.04		
6 0.1	563E+09	-94.98	0.77852+09	37.70	0.9598E+09	50.07		
7 0.1	5575+09	-90.00	0.7777E+09	38.86	0.9599E+09	49.26		
3 O.1	1145+09	-127.45	0.7859E+09	38.38	0.9531E+09	49.73		•
9 0.1	697E+09	-85,41	0.78335+09	44.12	0.9532E+09	45.63		
10 0-1	5575+09	-90.00	0.7868E+09	37+24	0.9531E+09	50.55		• • •
11 0.1	693E+09	-65.49	0.78592+09	38.38	0.9531E+09	49.73		
12 0.3	847E+0'8	-90.00	0.82615+39	35.20	0.9193E+09	52.29		
13 0.1	958E+09	-90.00	0.32275+09	41.51	0•9185E+09	47.88		
14 J+2(	0958+09	-35.29	0•7543E+09	36.29	0.97295+09	50.71		;
15 0.2	978E+09	-44.53	0.7657E+09	35-10	0.97278+09	51.50	حـو.	1 <b>/ /1</b> 1 /
16 0.93	850E+08	-43.62	0.8810E+09	29.98	0.8779E+09	50.12		
17 0.70	3045+08	-124-17	0.9733E+09	40.28	0.8703E+09	49.75		
18 0.8	7795+03	-154.22	0.8109E+09	44.15	0.92885+09	45.66		
19 0.33	314E+03	-133.90	0.8111E+09	47•44	0•9288E+09	43.07		
20 0.38	316E+03	-164.75	0•8455E+09	44•97	0+8965E+09	45.03		
21 0.88	346E+08	-90.00	0+84558+09	46.01	0-8965E+09	44.09		
22 0.52	262E+08	-134.42	0.3227E+09	41.51	0•9186E+09	47.88		
23 0.44	¥72E+08	-90.00	0.8221E+09	44•96	0.91845+09	45.03		
24 0.31	L64E+03	-135.57	0.8463E+09	43.32	0.8954E+09	46.53	į	
25 3.98	873.E+08	-53.54	0•8466E+D9	45.05	0.8953E+09.	<b>44</b> •95		
							,	•

FILE: SEXHAR OUTPUT

A1 BUET COMPUTER CENTRE, DHAKA

- 106 -

26	0.4472E+03	_90 <b>→</b> 00	0+3478E+09	40.03	0.8959E+09	49.51	• ,
27	0.5029E+08	-62.80	0-3468E+09	43.32	0.8954E+09	46.53	
28	0.2175E+08	-90.00	0.85968+09	.42.52	0.8332E+09	47.37	·
29	0+1053E+09	-37.39	0+8594E+09	44.20	0.8830E+09	45.76	
30	0.49918+08	-28.58	0+8829E+09	. 39•78	0.8515E+09	50.45	
31	9.4339E+08	-32.95	0.8822É+09	42.63	0.8505E+09	47.48	
32	J <b>.2503E+08</b>	-23.59	0•3734E+09	42.95	0.8544E+09	47+20	
33	0.1508E+09	-138.30	0.8733E+09	43.33	0.85425+09	46.20	
34	0+1735E+08	-164.93	0.3596E+09	45•04	0.8323E+09	44.96	
35	0.6989E+07	-139-47	0.8595E+09	45•45	0.88285+09	44.57	
36	0.7975E+07	-154.12	- 0.8659E+09	45.03	0.8765E+09	44.97-	
37	0.31835+07	-135.70	0.36592+09	45+20	0.8765E+09	44•31	
33	0.35155+07	-160.15	0•3688E+09	45.00	0.8737E+09	45,00	• •
39	0.13586+07	-113.47	0•3688E+09	45.08	0.9737E+09	44.92	
4)	0.1302E+07	-135.01	0.87025+09	44•98	0.8722E+09	45+02	
41	0+21755+03	-90 <b>+</b> 00	0.87028+09	<b>45.</b> 00	0.87225+09	45.00	, · ·
42	0.15398+98	-137.03	0.8594E+09	44•20	0.8330E+09	45.76	
43	0.10475+08	-33-63	0.85932+09	45.03	0.3330E+09	44.27	
44	0.7419E+07	-135.73	0.86552+09	44+62	0+8769E+09	45.37	
45	0.51795+07	-90.00	0•8655 <u>E</u> +09	45.00	0.8769E+09	45+00	
46	3.3532E+07	-128.93	0+8684E+09	44.81	0.8740E+09	45.18	•
47	0 <b>.</b> 2852E+07	-90.00	) 0+8684E+09	44.98	0.8740E+09	45.02	•
48	0.2308E+07	-105.30	0+8697E+09	44•90	0.8728E+09	45.10	•
49	0.2450E+08	-52.62	0+8697E+09	44.94	0.8728E+09	45.05	н -
50	0.1049E+08	-87.97	0+3656E+09	43.81	0.8770E+09	46+17	
⁻ 51	0+1176E+08	-53.14	0-8655E+09	44•52	0.8769E+09	45.37	
52	0.5180E+07	-87•99	0•8684E+09	44•43	0+8741E+09	45.56	
53	0.5674E+07	-65+90	0.8684E+09	44.81	0•87405+09	45•18	

FILE	SEXHAR	OUTPUT ,	A1 BUEF COM	PUTER CI	ENTRE, DHAKA		n o constante Internetionale Nationale
		•		-		- 10	7 – .
5	4 J.2853E+	07 -89.93	0.8697E+09	44.73	0.8728E+09	45.27	•
5	5 0.29355+	07 - 77.25	0.8697E+09	44.90	0.3728E+09	45.10	1)
· 5	6 0 <b>.</b> 2215E+	07 -90.00	0.8700E+09	44.37	0.8724E+09	45.13	
5	7 0 <b>.</b> 1953E+	-08 -30.92	0.87005+09	44+92	0.8724E+09	45.08	·
5	3 0•1215€+	-03 -21.96	0.87498*09	44.05	0.8576E+09	45.97	
5	9 0 <b>.</b> 3918E+	07 -30.53	0.3749,2+09	44•44	0.85766+09	45.57	
60	0.57455+	07 -22.33	0.37295+09	44•55	0.8695E+09	45.44	
6	L 0.3952E+	07 -33.43	0.8729E+09	44•73	0.8695E+09	45.27	
63	2 0.2605E+	07 -27.25	0-3718E+09	<u>44+80</u>	0.8706E+09	45+20	
63	0.1507E+	0752.35	0.8718E+09	44.87	0.8705E+09	+5-13	• • •
54	0.1125E+	07 -54.37	0.8711E+09	44.92	0.8714E+09	-45 <b>.</b> 08	· ·
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EZ1 - Electric Stress (D.C. case)
EA1 - Electric Stress Angle (D.C. case)
EZ2 - Electric Stress (AC, negative maximum to positive maximum
EA2 - Electric Stress Angle (AC, negative maximum to positive maximum)
EZ3 - Electric Stress (AC, positive maximum to negative maximum
EA3 - Electric Stress Angle (AC, positive maximum to negative maximum)

LEGEND---

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FIN	NITE ELEMENT DESIGN OF PIN-TYPE INSULATOR	
NODE	POTENTIAL AT DIFF HUDE(V)	· · · · · · · · · · · · · · · · · · ·
1	11000.00	· ,
. 2	11000.00	⁻
3	11000.00	<u>,</u>
. 4	9120.85	•
5	8791.67	
· 5	8736-80	
7	8581.93	
8	• 7858•87	•
9	5252+17	· · · · · · · · · · · · · · · · · · ·
10	. 2505.52	
11	1202.99	
12	954.43	
. 13	913.33	
14	915.04	
15	913.58	
. 16	913.45	•
17	913.45	•
. 18	913.34	· · · ·
19	913.11	· · · · · ·
20	911.46	• •
21	911.46	
22	· 908.17	
23	893.08	·
: 24	632.60	
25	359.65	
. 26	303.13	

$\begin{array}{cccccccccccccccccccccccccccccccccccc$	'FILE:	VIPU DUTPUT	A1 BUET COMPUTER CENTRE: DHAKA : - 109 -
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	27	293.48	
29, 290.72 30, 289.34 31, 279.70 32, 0.00 33, 0.00 34, 0.00 35, 0.00 36, 5474.53 39, 9285.50 40, 8654.49 41, 8366.62 42, 5449.17 43, 5322.15 44, 2220.62 45, 1054.82 46, 1417.09 47, 581.56 48, 905.03 49, 988.88 50, 365.40 51, 919.98 52, 251.44			);;t.
30       289.34         31       279.70         32       0.00         33       0.00         34       0.00         35       0.00         36       0.00         37       0.00         38       5474.59         39       9285.50         40       8654.49         41       8366.62         42       5449.17         43       5322.15         44       2220.62         45       1054.82         46       1417.09         47       581.56         48       905.03         49       988.88         50       365.40         51       919.98         52       251.44			
31 $279.70$ $32$ $0.00$ $33$ $0.00$ $34$ $0.00$ $35$ $0.00$ $35$ $0.00$ $37$ $0.00$ $38$ $5474.53$ $39$ $9285.50$ $40$ $8654.49$ $41$ $8366.62$ $42$ $5449.17$ $43$ $5322.15$ $44$ $2220.62$ $45$ $1054.82$ $46$ $1417.09$ $47$ $581.56$ $48$ $905.03$ $49$ $988.88$ $50$ $365.40$ $51$ $919.98$ $52$ $251.44$			
$\begin{array}{cccccccccccccccccccccccccccccccccccc$		1	
33 $0.00$ $34$ $0.00$ $35$ $0.00$ $35$ $0.00$ $37$ $0.00$ $38$ $5474.59$ $39$ $9285.50$ $40$ $8654.49$ $41$ $8366.62$ $42$ $5449.17$ $43$ $5322.15$ $44$ $2220.62$ $45$ $1054.82$ $45$ $1417.09$ $47$ $581.56$ $48$ $905.03$ $47$ $988.88$ $50$ $365.40$ $51$ $919.98$ $52$ $251.44$	_		
34       0.00         35       0.00         36       0.00         37       0.00         38       5474.53         39       9285.50         40       8654.49         41       8366.62         42       5449.17         43       5322.15         44       2220.62         45       1054.82         46       1417.09         47       581.56         48       905.03         47       988.88         50       365.40         51       919.98         52       251.44			
35       0.00         37       0.00         38       5474.59         39       9285.50         40       8654.49         41       8366.62         42       5449.17         43       5322.15         44       2220.62         45       1054.82         46       1417.09         47       581.56         48       905.03         47       988.88         50       365.40         51       919.98         52       251.44		•	• • • • • • • • • •
35       0.00         37       0.00         38       5474.59         39       9285.50         40       8654.49         41       8366.62         42       5449.17         43       5322.15         44       2220.62         45       1054.82         46       1417.09         47       581.56         48       905.03         49       988.88         50       365.40         51       919.98         52       251.44			
$\begin{array}{cccccccccccccccccccccccccccccccccccc$		•	
$\begin{array}{rrrrrrrrrrrrrrrrrrrrrrrrrrrrrrrrrrrr$	•		
39       9285.50         40       8654.49         41       8366.62         42       5449.17         43       5322.15         44       2220.62         45       1054.82         46       1417.09         47       581.56         48       905.03         47       988.88         50       365.40         51       919.98         52       251.44	1		
40       8654.49         41       8366.62         42       5449.17         43       5322.15         44       2220.62         45       1054.82         46       1417.09         47       581.56         48       905.03         49       988.88         50       365.40         51       919.98         52       251.44	<b>39</b>		
<ul> <li>41 8366.62</li> <li>42 5449.17</li> <li>43 5322.15</li> <li>44 2220.62</li> <li>45 1054.82</li> <li>46 1417.09</li> <li>47 581.56</li> <li>48 905.03</li> <li>49 988.88</li> <li>50 365.40</li> <li>51 919.98</li> <li>52 251.44</li> </ul>			
<ul> <li>43 5322.15</li> <li>44 2220.62</li> <li>45 1054.82</li> <li>46 1417.09</li> <li>47 581.56</li> <li>48 905.03</li> <li>49 988.88</li> <li>50 365.40</li> <li>51 919.98</li> <li>52 251.44</li> </ul>	· 41	•	
<ul> <li>43 5322.15</li> <li>44 2220.62</li> <li>45 1054.82</li> <li>46 1417.09</li> <li>47 581.56</li> <li>48 905.03</li> <li>49 988.88</li> <li>50 365.40</li> <li>51 919.98</li> <li>52 251.44</li> </ul>	. 42	5449•17	
<ul> <li>45 1054.82</li> <li>46 1417.09</li> <li>47 581.56</li> <li>48 905.03</li> <li>47 988.88</li> <li>50 365.40</li> <li>51 919.98</li> <li>52 251.44</li> </ul>	43	5322.15	
<ul> <li>45 1417.09</li> <li>47 581.56</li> <li>48 905.03</li> <li>49 988.88</li> <li>50 365.40</li> <li>51 919.98</li> <li>52 251.44</li> </ul>	44	2220.52	
<ul> <li>47 581.56</li> <li>48 905.03</li> <li>49 988.88</li> <li>50 365.40</li> <li>51 919.98</li> <li>52 251.44</li> </ul>	45	1054.82	
<ul> <li>48 905.03</li> <li>47 988.88</li> <li>50 365.40</li> <li>51 919.98</li> <li>52 251.44</li> </ul>	45	1417.09	
<ul> <li>47 988.88</li> <li>50 365.40</li> <li>51 919.98</li> <li>52 251.44</li> </ul>	ʻ 47	581.56	
<ul> <li>47 988.88</li> <li>50 365.40</li> <li>51 919.98</li> <li>52 251.44</li> </ul>		905.03	
51 919.98 52 251.44		988.88	4
52 251.44	· 50	365 • 40	
	51	919.98	
53 914.07	52	251.44	, , , , , , , , , , , , , , , , , , ,
	53	914.07	· · ·

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AL BUET COMPUTER CENTRE, DHAKA - - 110 -

ELECTRICAL STRESS DISTRICTION IN DIN T

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ELE	CTRICAL STR	ESS DIST	RIBUTION I	N PIN-TY	PE INSULATO	IR	
	EZ1	EA1	E22	ÉA2	EZ3	EA3	
1	0+115E+09	5.50	0•938E+09	41.76	0.802E+09	49.24	·
2	0.246E+08	25.57	0.889E+09	44•62	0.853E+09	45.41	
3	0.431E+08	-12-27	0.3896+09	43.23	0.853E+09	46.90	
4	0.9855+07	-68.20	0.868E+09	44.54	0.874E+09	45.46	
5	0+409E+07	-115.57	0+8685+09	44.93	0.874E+09	· 45.07	-
6	0 <b>.</b> 114E+09	0.00	0.9322+09	41.38	0•809E+09	49.63	
7	0+185E+09	-19.32	0.932E+09	37.50	0.812E+09	54,56	
8	ó.743E+08	-55.51	0.8615+09	41.22	0.882E+09	48.62.	
. 9	0•530E+08	-57.45	0.9612+09	41.82	0.3825+09	48.05	,
10	0.531E+08	-91.98	0.841E+09	43.05	0.9018+09	46.73	
i1	0.360E+09	-90.00	0.683E+09	25+51	0.105E+10	53.88	
12	0.362E+09	-89.73	0.683E+09	25.34	0.104E+10	53.95	
. 13	0•402E+09	-64.20	0.795E+09	21.57	0.967E+09	60.86	
14	0+202E+09	\$⇒37•59	0.765E+09	35+67	0•972E+09	51.15	
15	0+205E+09	-ġ0.47	0.7828+09	34.85	0.959E+09	52.07	
15	0.173E+09	-33.45	0.7795+09	37.34	0 <b>.</b> 959E+09	50.33	
17	0-357E+09	-89.73	0.685E+09	25.71	0+104E+10	53.89	
- 13	0.355E+09	-90.00	0.685E+09	25+33	0•104E+10	53.80	• •
19	0.355E+09	-88.63	0.691E+09	25.64	0.104E+10	54.10	
- 20	0•253E+09	-125.70	0•665E+09	41.86 (	0.105E+10	46• 43	
21	0•205E+09	-39.70	0.7622+09	35.59 (	0 <b>•</b> 975E+09	51.10	
22	0.133E+09	-95.96	0.7605+09	37.68 (	0•976E+09	49.73	-
23	0.148E+09 -	-183.00	0.790E+09	51.22 0	•949E+09	40•48	
24	0.1055+09 -	-132.14 (	0.788E+09	44.69.0	•9492+09	45.23	ŧ
25	0•800E+08,-	-103.75	0.8185+09	42.65 0	•923E+09	46 • 90	
26	0.765E+08 -	-108.42 0	0.818E+09	43•07 b	•923E+09	46.56	

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		•	-	· ·					
	FILE:	NIPU .	OUTPUT	A1 BUET ;	COMPUTER	CENTRE, DH	1484 -	111 -	
	27	0.740E+08	-78.86	0.840E+09	41.69	.0•903E+09	47.92		
	28	0.703E+08	-180.00	0.833E+09	47•72	0.909E+09	42.66		· · ·
	29	0.500E+08	-140.95	0.932E+09	45+28	0.909E+09	44•75		·
	30	0.398E+08	~127.44	0.841E+09	44.72	0.901E+09	45•25		ļ
	31	0.404E+08	-122.23	0.8415+09	44.52	0.901E+09	45•42		
	32	0.370E+08	-67.31	0.8605+09	43.23	0.8825+00	46.70		
	33	D•153E+08	-111.39	0.8600+09	44.68	0.8825+09	45.30		
	34	• •		0.3655+09	44•40	0.878E+09	45.59		•
	35			0.850E+09	46:45	0.3922+09	43.67		1
	36		•	0.850E+09	45.38	0.892E+09	44.65		
÷	37	·		0•852E+09	45.27	0.891E+09	44.75		
	38			0.852F+09	44.98	0.891E+09	45,01		
	39			0.858E+09	44•54	0.8842+09	45.44		н
	40			0.858E+09	45.40	0•884E+09	44.62		
	41			0.8692+09	44.69	0.873E+09	45.31	9	• • •
	42			0•869E+09	44.98	0•873E+09	45.02		
	4 <b>3</b>			0.870E+09	44.91	0•872E+09.	45.09		
	44		•	0.3588+09.	45.90	0.384E+09	44.15		:
	•	0.184E+08				0•884E+09	44•68		· -
		0+193E+08		•		0•885E+09	44+65		· .
		0.196E+08				0•885E+09	45.38		· ·
		0.205E+07				0•872E+09	44•90		!
		0-557E+06				0•872E+09	<b>45</b> ∎00		
		0•407E+05		•		0•871E+09	45.02		1
		0.229E+06 -				0•871E+09	45.01		1
		0+169E+08				•879E+09	44.34		j .
•		0•746E+07		u•858 <u>5</u> +09		<b>•874</b> E+09	44.68		
				3	·		•		
	-					· .•	·	]	
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FILE: NIPU 🔴 DUTPUT

		· · · ·			
54	<b>0.408E+07 −112.5</b> 2	0•868E+09~	44•92 D•874E+09	45 - 08	
55	0.451E+06 -209.14	0.871E+09	45.02 0.871E+09	44.98	
56	0.1278+06 -149.58	0.871E+09	45.00 0.371E+09	45•00	
57	0.911E+05 -134.94	0.871E+09	45.00 0.871E+09	45.00	
. 58	0.9858+05 -112.62	0.371E+09	45.00 0.871E+09	.45•00	i 
59	0.1595+07 -202.38	0.871E+09	45.08 0.872E+09	44+92	•
60	0.701E+06 -113.20	0.871E+09	44.99 0.872E+07	45.01	· ·
61	0.1136+06 -183.00	0.871E+09	45.00 0.871E+09	45.00	
· 62	0.4086+05 -201.82	0.871E+09	45.00 0.871E+09	45.00	
63	0.1698+03 -115.59	0.871E+09	45.00 0.8712+09	45•00	<i>.</i>
64	0.2918+05 -198.44	0.871E+09	45.01 0.871E+09	44.99	•
65 [,]	0.1308+06 -135.01	0.871E+09	45.00 0.871E+09	45.00	
66	0.758E+04 -130.00	0.871E+09	45.00 0.871E+09	45.00	· L.

LEGEND		
EZ1	-	Electric Stress (D.C. case)
EA1		Electric Stress Angle (D.C. case)
EZ2	-	Electric Stress (AC, negative maximum to positive maximum
EA2	-	Electric Stress Angle (AC, negative maximum to positive maximum)
EZ3	-	Electric Stress (AC, positive maximum to negative maximum
EA3	-	Electric Stress Angle (AC, positive maximum to negative maximum)

MECHANICAL STRESS DISTRIBUTION IN PIN-TYPE INSULATOR

		inclusion bisincition in	ти гти-т	FE INSULAT	UK ,	<b>,</b>
	TT1	TT1 TT2	ANG2	TT3	ANG3	, ,
1	0.1745E+06	-79.01 0.1166E+08	-6.47	0.8536E+07	8.47	· .
2	0.8004E+04	-36.87 0.1049E+08	-0.75	0.9657E+07	0.81	
3	0.2462E+05	-65•46_0•10495+08	-3.54	0.9560E+07	3.80	
4	0.12908+04	45.40 0.1000E+08	-0.92	0.1014E+08	0.91	
5	0.22248+03	36.87 0.1000E+08	-0.13	0.1014E+08	0.13	
6	0.1729E+06	-90.00 0.1152E+08	-7.24	0.8674E+07	9-26	
7	0•4552E+06	-51.36 0.1153E+08	-14.99	0.8757E+07	19.12	
8	0.7333E+05	21.03-0.9842E+07	-7.55	0+1032E+08	7.25	
. 9	0.52595+05	24.89 0.9838E+07	-6.35	0•1032E+08	6.09	
10	0.3741E+05	85.05 0.9387E+07	-3.89	0.1077E+08	,3.46	na an a
11	0.1720E+07	90.00 0.6182E+07	-38.97	0.1449E+03	17.75	
12	0.1735E+37	89.46 0.6191E+07	- 39•31	0•1448E+08	17.92	· · · ·
13	0.2141E+07	38.41 0.8392E+07	-46.85	0.1241E+08	31.71	
•1,4	0.5408E+05	35.19 0.7792E+07	-18.65	0.12528+08	· 12.29	•
15	0.5551E+05	70.93 0.8113E+07	-20.29	0.1221E+08	14.15	
16	0.3975E+06	85.91 0.8058E+07	-15.33	0+1221E+08	10.65	
17	0•1690E+07	37.46 0.6228E+07	-38.58	0.14435+08	17.77	
18	0•1675E+07	90.00 0.5220E+07	-38.24	0 <b>.</b> 1444E+08	17.61	
19	0-1676E+07	87.27 0.6327E+07	-38.71	0•1433E+08	18.19	· · ·
20	0.8492E+06	18.60 0.5851E+07	-6.29	0.14568+08	2.87	
21	0•5603E+06	87.40 0.7704E+07	-18.81	0.1262E+08	12.20	:
22	0•4454E+06	78.09 0.7659E+07	-14-63	0.1263E+08	9•47	
23	<b>0.2892E+06</b>	-90.00 0.8236E+07	12.43	0.1195E+08	-9.05	
24	0•1458E+05	5.71 0.8233E+07	-0.62	0.11955+08	0.45	•
25	0•8493E+05	62.51 0.8871E+07		0•1130E+08 ·		: .
26	<b>0.7752E+05</b>	53.15 0.8869E+07		0.1130E+08	3.13	- -
27	<b>0.7258E+05</b>	57.72 0.9352E+07		0.1081E+08	5.84	
28	<b>0.</b> 5563E+05	-90.00 0.9199E+07		0.1096E+03	-4.67	
	. ·		<b>-</b> .			;

FILE: NIPU

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29 0 <b>.</b> 3320E+05	5 -11.72 0.9191E+07	0.55 0.1096E+08	-0.48
30 0.2098E+05	15.13.0.9373E+07	-0.55 0,1077E+08	0.50
31_0•2167E+05	25.43 0.9373E+07	-0.95 0.1077E+08	0.85
32 0.1819E+05	44.61 0.9823E+07	-3.54 0.1032E+08	3.39
33 0.31248+04	47.23 0.9320E+07	~0.64 0.1032E+08	0.61
34 0•2778E+04	71.72 0.9920E+07	-1.20 0.1022E+08	1.17
35 0 <b>•1</b> 997E+05	-90.00 0.95352+07	2.90 0.1056E+08	-2.55
36 0 <b>.</b> 1067E+05	-29.15 0.9584E+07	0.75 0.1056E+08	~0.69
37 0.8917E+04	-22.74 0.9619E+07	0.54 0.1052E+08	-0.50
38 0•8571E+04	1.33 0.9619E+07	-0.03 0.1052E+08	0.03
39 0•4300E+04	55.78 0.9772E+07	-0.92 0.1037E+08	0.88
40 0.45518+04	-49.61 0.9772É+07	0.31 0.1037E+08	-0.77
41 3.5124E+33	50.44 0.1002E+08	-0.52 0.1012E+09	0.62
42 0.11295+03	14.04 0.1002E+08	-0.04 0.10122+08	0.04
43 0•7029E+02	84.53 0.1004E+08	-0.17 0.1010E+08	0.17
44 J.7931E+04	-99.00 0.9764E+07	1.30 0.1038E+08	-1.70
45 0.4516E+04	-40.86 0.9763E+07	0.57 0.1038E+08	-0.63
46 J•4967E+04	-43.28 0.97518+07	0.74 0.10395+08	-0.70
47 0•5093E+04	46.75 0.9751E+07	-0.81 0.1039E+08	0.77
48 0•5621E+02	-31•41 0•1006E+08	0.20 0.1008E+08	-0.20
49 0.4118E+01	0.02 0.1006E+08	0.00 0.1008E+08	0.00
50 0.2220E+01	58.82 0.1007E+08	-0.04 0.1007E+08	0•04
51 J•5956E+00	57.36 0.1007E+08	-0.01 0.1007E+03	0.01
52 0•3782E+34	-77.17 0.9883E+07	1.36 0.1026E+08	-1.31
53 0•7391E+03	-50.73 0.1000E+08	0.66 0.1014E+08	-0.65
54 0.2212E+03	44•95 0•1000E+08	-0.15 0.1014E+08	0.16
55 D.2698E+01	-31.71 0.1007E+08	0.04 0.1007E+08	-0.04
	· .		

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FIL	E: NIPU	JUTPUT	A1 BUET	COMPUTER	CENTRE, DHA	KA CMST		
, 55	<b>J+2150E+00</b>	-29.15	0.1007E+08	0.00	0.1007E+08	0.00		· ;
57	0.1101E+00	0.12	0.1007E+08	0.00	0.10078+08	0.00		i
58	0.1237E+00	44.77	0.1007E+08	0.00	0.1007E+03	0.00		,
59	0.3795E+02	-45-24	0.1006E+08	0.15	0.1003E+08	-0.16		
60	<b>0.5512E+01</b>	43.60	0.1006E+08	-0.03	0.1008E+08	0.03		
61	0.1599E+00	-99+00	0.1007E+08	0.01	0.1007E+08	-0.01		
62	0.22098-01	-45•35	0.1007E+08	0.00	0.1007E+08	0.00		
63	0.38015-02	35.82	0.1007E+08	0.03	0+1007E+08	0.00		
64	0•1123E+01	-53.13	0.1007E+08	0.03	0.1007E+08	-0.03		·
65	0+2246E+00	-0.01	0.1007E+08	0.00	0.1007E+08	0.00	·	
66	0.7615E-03	-93.00	0.1007E+08	0.00	0.10075+08	0.00		

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00 0	•7615	5E-03 -90.0	0 0.1007	'E+38	0.0	0.1007	'E+08	0.00		
		•	•		-			•	•	· · · · · ·
		· _								
									•	
LEGEND		, ,								
		• ·				-		-		
TI-1	-	Mwchanical	Stress	(D.C.	case)					
ANG1	_	Mechanical							·	
TT2	<b>_</b> '							· .		-
7 1 dan		Mechanical maximum	516855	(AC, r	negati	ve maxim	um to p	ositive	2	
ANG2	-	Mechanical positive ma	Btress	Angle	(AC,	negative	maximu	m to		-
		hostriad W	44 X BIUM7							
ттз	_	Mechanical Maximum	•	(AC, p	ositi	V@ maxim	um-to n	egative	2	
TT3 ANG3	- - -	Mechanical	Stress Stress						2	
•	-	Mechanical maximum Mechanical	Stress Stress						2	
•	- -	Mechanical maximum Mechanical	Stress Stress						2	
• •	_	Mechanical maximum Mechanical	Stress Stress						2	·
• •	-	Mechanical maximum Mechanical	Stress Stress						2	· ·
• •	_	Mechanical maximum Mechanical	Stress Stress						2	•
• •	-	Mechanical maximum Mechanical	Stress Stress						2	· · · ·
• •	-	Mechanical maximum Mechanical	Stress Stress						2	

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6029.39

5029.41

FINITE ELEMENT DESIGN OF DISC-TYPE INSULATOR POTENTIALS AT DIFF NODES

0.00 0.00 0.00 0.00 0 **.** 00 0.00 0.00 5556.95 5903.49 5993.45 6018.50 6024.98 6028.96 6029.27 6029.34 5029.37 5029.38 5029.38 22 - 6029.38

	FILE:	BIS	ͻυτͽυτ	A 1	BUET	COMPUTER	CENTRE.	DHAKA	- 117 -
	27	5029.45							
	28	5029.55							
· · ·	29	5031-14	,						
· .	- 30	6038.59						·	· · · · · ·
·	31	5043.54							
•	32	6044.25							1
, ·	33	6044.95							
-	34	6045.66							
	35	6050.63	1						
·	36	5129.12							
	37	6265.72							
	38	6599.45	`						
•	39	7626.07							·
	40	11000.00							•
	41	11000.00							
•	42	11000.00							
••	43	11000.00							
· · · · ·	44	11000.00							

45 11000.00 46 11000.00 47 11000.00

48 11000.00 49 5377.84 50 5255.69

 51
 4644.95

 52
 2324.14

 53.
 4651.60

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FILE:	BIS ·	συτρυτ	A1.	BUET	COMPL	ITER	CENTRE,	DHAKA	- 118 -
54	5282.28	- <u>.</u>			•			. •	
55 [°]	5477•58		•				•		
56	5628.10			•				•	
57	5034+91	•							
58	7511.59								
59	4372.10						`,		•
. 60	8139.37								
61	6419.87								
			,					• . •	
52	6058.58							· ·	· · ·
63	6031.77			·		,			<i>,</i>
64	5025.91			•					<b>,</b> ∎ •
65	6027.80						•	•	14. μ
66	6028.22								
67	6255.72							. · ·	
68	6029.39			•				• .	
69	5029.37				•	-			the construction of the state
70	5029+41		1						
71	5029.38	• • •							•
72	5029 <b>.</b> 38	-							

<b>IT1</b>	STRESS DISTRIBUTIC ANGL TT2	ANG2 TT3	ANGB
1 0.1535+07	90.00 0.144E+08	17.47 0.626E+07	-37.56
2 0.1565+07	87.28 0.144E+08	16.67 0.622E+07	- 35.93
3 0.156E+07	90.00 0.143E+08	17.22 0.532E+07	-36.41
4 0+125E+07	74•77 0•144E+08	13.21 0.615E+07	-28.21
5 0.123E+07	90.00 0.139E+08	15.91 0.566E+07	-30.87
6 0.632E+06	0.08 0.140E+08	0.01 0.635E+07	-0.02
7 0.633E+06	0.00 0.140E+08	0.00 0.635E+07	0.00
8 0.178E+07	87.45 0.147E+08	17.39 0.603E+07	-39.46
9 0 <b>.</b> 185E+07	90.00 0.146E+08	18.16 0.608E+07	-41.11

						•		
	10	0+187E+07	77.55	0.1516+08	15.49	0.557E+07	-38.77	
	11	0.224E+07	90.00	0+150E+08	19.21	0.580E+07	-47.31	· ·
	12	0.2555+07	43•85	0.1702+03	10.10	0.394E+07	-37.59	
	13	0+255E+07	-48.71	0.170E+08	-10.06	0•394E+07	37+48	
	14	0.534E+06	0.08	0•140E+08	0.01	0.634E+07	-0.02	
	15	0.124E+07	-90.00	0+1396+08	-15.92	0.665E+07	30.92	
	15	0.224E+07	-90.00	0.150E+08	-19.20	0.5815+07	47•24	•
	17	0.18.68+07	-77.09	0.1512+03	-15.36	0.556E+07	38.42	
	18	0.1252+07	-74.30	0•144E+08	-13.14	0.6135+07	28.18	2 - 1
	19	0.153E+07	-90.00	0 <b>.</b> 143E+08	-17-28	0.631E+07	36.55	:
	20	0.1948+07	-90.00	0.146E+08	-18.11	0.509E+07	40.35 -	
•	21	0.1725+07	-85.85	0-148E+08	<b>1</b> 16.87	0.602E+07	38.20	
	22	0.153E+07	-85.67	0.145E+08	-16.40	0.614E+07	35.89	· ·
	23	0.1592+07	-90.00	0.145E+08	-17.66	0.621E+07	38.51	
	24	0.172E+07	-90.00	0.1456+08	-17.75	0.618E+07	38•94	
	25	0.1535+07	- 86 • 72	0•145E+08	-16.77	0+613E+07	36.93	
	25	0.1698+07	-85•78	0•146E+08	-15.98	0.508E+07	37.94	12 <b>#</b>
	27	0.178E+07	-90.00	0.145E+08	-17.95	0•613E+07	39.97	
	28	0.153E+07	-90.00	0.144E+08	-17.45	0•626E+07	37.50	
	29	0.1418+07	-80.45	0•144E+08	-14.80	0•614E+07	32.04	
	30	0.1795+07	-81.53	0•149E+08	-16+14	0+579E+07	38.42	· .
	31	0.203E+07	-90.00	0 <b>.</b> 148E+08	-18.58	0.594E+07	44.01	
	32	0.140E+07	-90.00	0.141E+08	-16.62	0.6478+07	33.72	
				0•142E+08			13.89	· · ·
				0.161E+08			38.09	
	35	0.1752+07	32.48 (	0•163E+08	ó•14 <u>(</u>	0•443E+07 -	19.08	: *
	36	0•138E+07	73.71 (	0.135E+08	19.58 (	D.710E+07 -	35•46	

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37	0.7065+06	-90+00	0.130E+08	-12.98	0+738E+07	21.38
38	0.5912+06	-65.10	0.130E+08	-8.31	0+729E+07	13.74
39	0•431E+06	-63.11	0.128E+08	-7.51	0.7456+07	12.18
.40	0.315E+06	-5+99	0.128E+08	-0.65	0.741E+07	1.04
41	0•159E+05	42.20	0.108E+03	10.02	0.938E+07	-11.33
. 42	0.227E+05	21.04	0+108E+08	0.72	0+935E+07	-0.81
43	0.2268+05	21.77	0.102E+03	4•05	0.994E+07	-4.15
44	0.105E+04	57•98	0.102E+08	0.43	0.9935+07	-0.44
45	0•145E+04	19.92	0+101E+03	1.04	0.100E+08	-1.04
46	0.543E+02	69•54	0.1015+08	0.13	0.100 <u>±+08</u>	~0.13
47	0.993E+02	14+68	0•101E+08	0.27	0.101E+08	-0.27
. 48	0.5328+01	67.01	0.101E+08	0.05	0.101E+08	-0.05
49	0•759E+01	20.24	0•101E+08	0.08	0.101E+08	-0.08
50	0.630E+00	75.15	0.101E+03	0.02	0.101E+03	-0.02
51	0.652E+00	64•31	0.101E+08	0.02	0.101E+08	-0.02
52	0•493E+06	-69.53	0.121E+08	-13.62	0+825E+07	19.02
⁻ 53	0.1892+06	-56.69	0.111E+08	-9.78	0•910E+07	11.61
54	0.641E+05	-70.14	0.111E+08	-3•71	0.907E+07	4.41
55	0•920E+04	- 35 • 85	0.105E+08	-0.79	0.963E+07	0.85
56	0•888E+04	-28.85	0-105E+08	-0.63	0.963E+07	0.58
57	0.238E+04	<b>68</b> •85	0•103E+03	0.75	D.987E+07	-0.78
58	0.166E+04	-19.04	0.103E+08	-0.18	0.987E+07	0.19
59	0.562E+03	83.11	0.102E+08	0.43	0.998E+07	-0.44
60	0•400E+03	-55.04	0.102E+08	-0.25	0.998E+07	0.26
61	0.353E+02	81.25	0•101E+08	0+13	0•101E+08	-0.13
62	0.1548+02	-6.31	0.101E+08	-0+01	0.101E+08	0.01
63	0•6888#+01	85•52	0•101E+08	0.05	0.101E+08	-0.05
64	0.378E+01-	-47 <u>.</u> 27	0.101E+08	-0.02	0-101E+08	_`0 <b>.</b> 02
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65 0.534E+00 61.57 0.101E+08	0.02 0.101E+08 -	0.02	
65 0.170E+00 -49.54 0.101E+08	0.00 0.101E+08	0.00	
67 0.258E-01 35.05 0.101E+08	0.00 0.101E+08	0.00	
68 0.235E-02 -9.53 0.101E+08	0.00 0.101E+08	0.00	· · ·
69 0.127E-02 32.78 0.101E+08	0.00 0.101E+08	0.00	
70 0.105E-03 22.62 0.101E+08	0.00 0.101E+08	0.00	
71 0.739E-04 77.32 0.101E+03	0.00 0.101E+08	0.00	· .
72 0.658E+04 -90.00 0.104E+08	-1.56 0.979E+07	1.53	i S
73 0.110E+04 -90.00 0.102E+08	-0.65 0.996E+07	0.66	• • •
74 0.100E+02 -45.19 0.101E+03	-0.08 0.101E+08	0.08.	
75 0.172E+01 43.56 0.101E+08	0.01 0.101E+38	-0.01	• •
76 0.297E+00 -53.00 0.101E+08	-0.01 0.101E+08	0.01	•
77 0.591E-01 0.63 0.101E+08	0.00 0.101E+08	00.00	· .
78 0.189E-02 -25.78 0.101E+08	0.00 0,101E+08	0.00	
79 0.113E-03 -36.87 0.101E+08	0.00 0.101E+08	0.00	
<ul> <li>80 0.550E−04 −10.39 0.101E+08.</li> </ul>	0.00 0.101E+09	0.00	
81 0.586E-04 -30.51 0.101E+03	0.00 0.101E+08	0.00	: 
82 0.153E-04 61.93 0.101E+08	0.00 0.101E+08	or.∎00	· · ·
83 0.451E-05 -36.87 0.101E+08	0.00 0.101E+08	0.0.0	
84 0.902E-05 90.00 0.101E+08	0.00 0.101E+08	0.00	· ·
85 0.902E-04 -90.00 0.101E+08	0.00 0.101E+08	0.00	
86 0•442E-04 -90•00 0•101E+08	0.00 0.101E+08	0.00	1
87 0.721E-05 0.00 0.101E+08	0.00 0.101E+08	0.00	
88 0.000E+00 90.00 0.101E+08		. 0.00	(B)
89 0.000E+00 90.00 0.101E+08		0.00	
90 0.000E+00 90.00 0.101E+08		0.00	
91 0.000E+00 90.00 0.101E+08		000	
91 0.000 - 00 J0200 222			

-165	315	001501	A1 BUET	COMPUTER CENTRE,	DHAKA CMS	<b>.</b> .
			, -			·
92	0.000E+00	90 <u>.</u> 00	0.101E+08	0.00 0.101E+03	0.00	
93	0.000E+00	90.00	0.101E+03	0.00 0.101E+08	0.00.	

0.00 0.101E+08

0.00.

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## LEGEND

TT1	-	Mechanical Stress (D.C. case)
ANG1	` <b></b>	Mechanical Stress Angle (D.C. case)
TT2 ·	-	Mechanical Stress (AC, negative maximum to positive maximum
ANG2		Mechanical Stress Angle (AC, negative maximum to positive maximum)
ттз	-	Mechanical Stress (AC, positive maximum to negative maximum
ANG3	-	Mechanical Stress Angle (AC, positive maximum to negative maximum)

FILE: DISC DUTPUT

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## ELECTRICAL STRESS DISTRIBUTION IN DISC-TYPE INSULATOR

EZ1	EAI	EZ2	EAZ	5 5 2 3	EA3
1 0.351E+09	-90.00	0.104E+10	53.73	0.687E+09	26.22
2.0•343E+09	83•64	0.104E+10	53.34	0.685E+09	27.03
3 0.343E+09	-90.00	0.104E+10	53.61	0•590E+09	26•80
4 0.308E+09	82.39	0+104E+10	51.60	J•681E+09	30-89
5 0+305E+09	-90.00	0+1025+10	52.96	9.708E+09	29.57
6 0.218E+09	45.04	0.103E+10	45.01	0+592E+09	44.99
7 0.218E+09	45•00	0.103E+10	45.00	0•692E+09	45.00
8 0.366E+09	88•72	0.105E+10	53.59	0.574E+09	25.27
9 J•374E+09	90.00	0.1052+10	54.08	0.677E+09	24.45
10 0.3755+09	83.73	0.107E+10	52.75	0.648E+09	25.61
11 0.4118+09	-90.00	0.105E+10	54.61	0.6512+07	21.35
12 0.439E+09	69.43	0.113E+10	50.05	0≠545E+09	26.20
13 0.4398+09	20.54	0.1138+10	39.97	0•545E+09	53.74
14 0.219E+09	45.04	0.1038+10	45.01	0.691E+09	44.99
15 0.305E+09	0.00	0.102E+10	37.04	0.708E+09	50 <b>.</b> 46 ,
15 0.4115+39	0.00	0.1065+10	35.40	9.662E+09	58.62
17 0.3745+09	6.45	0.107E+10	37.32	0.648E+09	54.21
18 0.308E+09		0.1042+10	38.43	0•530E+09	59.09
19 J•345E+D9	0.00	0.1042+10	36.36	9•689E+09	53.33
20 0.3722+09	0.00	0.105&+10	35.94	0.677E+09	55.42
21 0.360E+09	2.07	0.105E+10	36.56	0•674E+09	54.10
22 0 <b>.</b> 345E+09	2.15	0.105E+10 1	36.80	0.580E+09	62.95
23 0.357E+09	0.00	0.104E+10	36+17	0.6845+09	54.26
24 D.350E+09		0.104E+10	36.12	0•683E+09	54.47
25 0 <b>.</b> 351E+09	1.64	0.105E+10	36.51	0.580E+09	63.46

FILE: DISC OUTPUT

A1 BUET COMPUTER CENTRE, DHAKA

、 ·				•	- 124 -
	_ 2610.357E+09	1.61 0.105E+10	36.51 0.677E+09	63.97	-
	27 0.365E+09	0.00 0.105E+10	36.02 0.680E+09	64.98	
	28° <b>0.351</b> E+09	0.00 0.104E+10	36.27 0.687E+09	63.75	• •
	29 0.325E+09	4.77 0.104E+10	37.60 0.680E+09	51.02	:
	30 0.367E+09	4.24 0.106E+10	36.93′0.661E+09.	64•21	•
	31 0.3918+09	0.00 0.106E+10	35+66 0+669E+09	67.01	
	32 0.3252+39	0.00 0.103E+10	36.69 J.699E+09	61.85	•
	33 0.251E+09	23.10 0.104E+10	41.64 0.682E+09	51.95	
	34 0.404E+09	14.11 0.110E+10	38.72 0.597E+09	64•05	,
• .	35 0.3642+09	51.24 0.111E+10	48.07 0.578E+Q9	35.46	•
	35 0.322E+09	-251.8 0.101E+10	54+84 0∔73ZE+09.	27.27	
	37 0.2315+09	0.00 0.989E+09	38.51 0.745E+09	55.69	
	38-0+194E+09	12.45 0.9902+09	40.84 0.741E+09	51.87	· ·
	39 0.180E+09	13.44 0.983E+09	41.20 0.749E+09	51.09	· · ·
	40 D.154E+09	42.00 0.9845+09	44+58 0+7475+09	45.52	•
	41.0 <b>.</b> 113E+0,9	-245.100.903E+09	50.01 0.841E+09	39.34	· · · · · ·
	42 J.414E+08	55.52 0.902E+09	45.36 D.840E+09	44.59	
	43 D.412E+08	-235.9 0.877E+09	47.02 0.865E+09	42.93	·
	44 0 <b>.</b> 891E+07	73.99 0.877E+09	45•22 0•865E+09	44.78	
	45 0.1055+03	-234.9 0.8735+09	45.52 3.870E+09	44.48	• •
	45 0.2205+07	79.77 0.873E+09	45.06 0.870E+09	44.94	,
	47 0.274E+07	-232.3 0.871E+09	45.14 0.871E+09	44.85	
	48 0 <b>.</b> 633E+06	-258.5 0.871E+09	45.03 0.871E+09	44.97	
	49 0.7565+06	-235.1 0.871E+09	45.04 J.871E+09	44.95	
	50 0 <b>.</b> 218E+05	-262.6 0.371E+09	45.01 0.871E+09	44•99	
	51 0.222E+06	-257.2 0.871E+09	45.01 0.871E+09	44•99	
	52 0.1935+09	-10.23 0.953E+09	38.19 0.788E+09	54.51	• •
-	53 0.1192+09	-15.65 0.915E+09	40•11 0•828E+09	50.81	
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54 0.6955+08	9•93 0•914E+0	9 43.14 0.8275+0	9 47.2	1		
55 D.263E+08	27.08 0.890E+09	9 44.61 0.852E+0				
56 0.259E+08	30.57 0.8902+09	•			•	
57 0.1345+03.	79.42 0.8805+09	45•38 J•S63E+0				
58 J+112E+08	35.48 0.880E+09	44.91 0.863E+0				
59 0.6515+07	86.56 J.875E+09			•		
60 0.5495+07	17.48 0.875E+07					
61 0.165=+07	-265.6 0.872=+09	45•06 J•870E+0				
62 0.108E+07	41.85 0.872E+09				i	
63 0.720E+05	-267.8 0.8725+09					
64 0.534E+05	21.36 0.872E+09				· , -	
·65 0.2015+05 -	-255.8 0.871E+09		·			
65 <b>3.113</b> E+05	20.23 0.871E+09	- 45.00 0.871E+09		1	1	
57 0.441E+05 -	-242.5 0.871E+09	45.00 0.371E+09				
68 0 <b>.</b> 133E+0 <u>5</u>	43.24 0.8715+09	45.00 0.871E+09			•	
69 0 <b>.</b> 93)E+04 -	241.4 0.8715+09	45•00 0•971E+09	-		• -	
· 70 J.282E+04	55.31 0.871E+09	45.00 0.871E+09		· .		
71 0.235E+04 -	253.7 0.9718+09	45.00 0.371E+00	45.00	•		
72 0.2235+08.	0.00 0.883E+09	44•22 0•859E+09		•		
73 0.912E+07	0.00 0.876±+09	44.58 0.866E+09				
74 0.859E+05 -	22.40 0.871E+09	44.96 0.371E+09				
75 0.350E+05	66•78 0•871E+09	45.01 0.371E+09		· .		
76 0 <b>.</b> 150E+06 -:	18.50 0.871E+09	44.99 0.871E+09	45.01			
77 3.5575+05	45.32 0.871E+09	45.00 5.871E+09	45.00			
78 0.119E+05 -3	31.61 0.871E+09	45.00 0.871E+09	45.00		· .	
79 D.291E+04 2	26.57 0.8715+09	45.00 0.371E+09	45.00			
80 0•204E+04 3	39.81 0.8715+09	45.00 J.871E+09	45.00			
	9.74 0.87IE+09		45.00		r 4	
	ı	·		:		

FILE: DISC

OUTPUT ' A1' BUET COMPUTER CENTRE, DHAKA .

		• `		•	- 126 -
82	0.1075+04	-255.9	0.871E+09	45.00 0.371E+09	45.00
83	0.5832+03	25.57	0.871E+09	45.00 0.871E+09	45.00
84	0.261E+03	-90.00	0.871E+09	45.00 0.871E+09	45.00
85	0 <b>.</b> 251E+04	0.00	0.871E+09	45.00 D.871E+09	45.00
86	0.1822+04	0.00	0.871E+09	45.00 0.8715+09	45.00
37	0.737E+03	-45.00	0.8715+09	45.00 0.871E+D9	45.00
. 88	0.0002+00	-90.00	0.871E+09	45.00 0.871E+09	45.00
. 89	0.00020+00	-90.00	0.871E+09	45.00 0.871E+09	45.00
90	0.000E+00	-90.00	0.871E+09	45.00 0.871E+09	45.00
91	0.0005+00	-90.00	0.871E+09	45.00 0.871E+09.	45.00
92	0.00025+00	-90.00	0.8712+09	45.00 0.871E+09	45.00
93	0.000E+00	-90.00	0.8715+09	45.00 0.871E+09	45.00
	•			· · · · ·	

LEGEND		
EZ1	-	Electric Stress (D.C. Case)
EA1	-	Electric Stress Angle (D.C. case)
EZ2	-	Electric Btress (AC, negative maximum to positive maximum
EA2		Electric Stress Angle (AC, negative maximum to positive maximum)
EZ3	-	Electric Stress (AC, positive maximum to negative maximum
EA3,		Electric Stress Angle (AC, positive maximum to

negative maximum)

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